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D-85354 Freising (DE)(54) **ACCELERATION SENSOR AND ITS MANUFACTURE.**

(57) An acceleration sensor having a novel structure by which acceleration measurement of high precision and reliability can be implemented. A monocrystalline silicon substrate (1) is joined to a monocrystalline silicon substrate (8) through an SiO₂ film (9). The monocrystalline silicon substrate (1) is a thin film. A cantilever (13) is formed on the monocrystalline silicon substrate (1). The thickness of the cantilever (13) in the direction parallel to the surface is smaller than that in the depth direction of the monocrystalline silicon substrate (1). The cantilever is

movable in the direction parallel to the surface of the substrate. The surface of the cantilever (13) and the surface of the monocrystalline silicon substrate (1) which faces the cantilever (13) are covered with an SiO₂ film (5) in order to prevent the electrodes of the capacitance type acceleration sensor from being short-circuited. A signal processing circuit (10) is formed on the monocrystalline silicon substrate (1) to process signals produced by the movement of the cantilever (13).

EP 0 591 554 A1

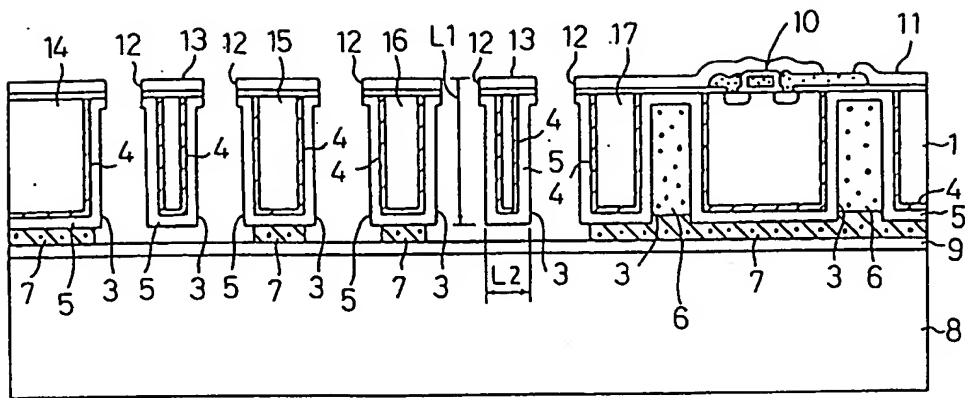


Fig. 2

TECHNICAL FIELD

The present invention relates to an acceleration sensor, and more specifically, a semiconductor type acceleration sensor suitable for air-bag system, suspension control system, or the like, for automobiles.

BACKGROUND TECHNIQUES

In producing a semiconductor type acceleration sensor, the movable part thereof has hitherto been prepared in such a way that it penetrates a singlecrystal silicon wafer. Accordingly, a size large enough to penetrate through the thickness of a wafer is required, and therefore, it has been difficult to miniaturize the acceleration sensor. In addition, in order to incorporate this sensor into a package, there has been required a relaxation part such as a pedestal in order to release the stress caused by the difference in coefficients of thermal expansion or the like.

However, in Nikkei Electronics, November 11, 1991 (No. 540), pp 223 to 231, there is illustrated an acceleration sensor produced by use of a surface micro-machining technique. That is, a thin polysilicon film is laminated on a silicon substrate, and thereafter, this polysilicon film is etched, whereby a beam movable parallel to the surface of the substrate is formed, so as to form a differential capacity type acceleration sensor. However, when a beam structure is formed by use of polysilicon, if a signal processing circuit is formed around the formed beam structure, the sensor characteristics become unstable. This is because the beam structure is formed of a polycrystalline and amorphous material, resulting in noticeable variation for every production lot. Accordingly, it is still desirable to form an acceleration sensor by surface micro-machining singlecrystal silicon.

Under such circumstances, the purpose of the present invention is to provide an acceleration sensor having a novel structure, by which high precision and high reliability can be realized.

In addition, another purpose of the present invention is to produce this acceleration sensor with a good yield rate during the production process thereof.

DISCLOSURE OF THE INVENTION

The gist of the first invention resides in an acceleration sensor, comprising a second singlecrystal silicon substrate bonded onto a first singlecrystal silicon substrate with an insulating film interposed therebetween the second singlecrystal silicon substrate being made of a thin film, a beam formed on at least either of said first and second

singlecrystal silicon substrates and movable in a direction parallel to the surface thereof, and a signal-processing circuit formed on at least one of said first and second singlecrystal silicon substrates for performing processing of signals produced by a movement of beam, caused by an acceleration.

In addition, the gist of the second invention resides in a process for producing an acceleration sensor, comprising; a first step of forming, on a main surface of a first singlecrystal silicon substrate, a groove with a predetermined depth for formation of a beam; a second step of forming, on the main surface of said first singlecrystal silicon substrate, a film of a polycrystalline silicon, an amorphous silicon or a mixture thereof so as to fill said groove with said silicon film, and smoothing (flattening) the surface of said silicon film; a third step of bonding the main surface of said first singlecrystal silicon substrate to a second singlecrystal silicon substrate with an insulating film formed thereon, said insulating film being interposed between said first and second singlecrystal silicon substrates; a fourth step of polishing the reverse side of said first singlecrystal silicon substrate to a predetermined degree, so as to make said first singlecrystal silicon substrate a thin film; and a fifth step of forming a signal-processing circuit on at least either of said first and second singlecrystal silicon substrates, and thereafter, removing by etching said silicon film of a polycrystal silicon, an amorphous silicon or a mixture thereof from said reverse side of said first singlecrystal silicon substrates, to form a beam.

In addition, the gist of the third invention resides in a process for producing an acceleration sensor, comprising; a first step of bonding a main surface of a first singlecrystal silicon substrate to a second singlecrystal silicon substrate with an insulating film formed thereon, said insulating film being interposed therebetween; a second step of polishing the reverse side of said first singlecrystal silicon substrate to a predetermined degree, so as to make the first singlecrystal silicon substrate a thin film; a third step of forming a groove with a predetermined depth for formation of a beam; a fourth step of forming, on the reverse side of said first singlecrystal silicon substrate, a film of a polycrystal silicon, an amorphous silicon or a mixture thereof, so as to fill said groove with said silicon film, and smoothing the surface of said silicon film; and a fifth step of forming a signal-processing circuit on at least one of said first and second singlecrystal silicon substrates, and thereafter, removing by etching said film of polycrystal silicon, amorphous silicon or a mixture thereof from the reverse side of the first singlecrystal silicon substrate, to form a beam.

In the first invention, when an acceleration is applied in a direction parallel to the surface of the bonded singlecrystal silicon substrates, the beam formed on the first or second singlecrystal silicon substrate moves. As this beam moves, signal processing is performed in the signal-processing circuit formed on the first or second singlecrystal silicon substrate.

In the second invention, as a first step, a groove of a predetermined depth for formation of a beam is formed on the main surface of the first singlecrystal silicon substrate, and as a second step, a film of a polycrystalline silicon, an amorphous silicon or a mixture thereof is formed on the main surface of the first singlecrystal silicon substrate, whereby the groove is filled with the silicon film, and the surface of this silicon film is flattened. Subsequently, as a third step, the main surface of the first singlecrystal silicon substrate is bonded to a second singlecrystal silicon substrate having an insulating film formed thereon, said insulating film being interposed between the first and second singlecrystal substrates, and, as a fourth step, the reverse side of the first singlecrystal silicon substrate is polished to a predetermined degree, whereby the first singlecrystal silicon substrate is made into a thin film. Subsequently, as a fifth step, a signal-processing circuit is formed on the first or second singlecrystal silicon substrate, whereafter the polycrystalline, amorphous or mixed silicon film is removed by etching from the reverse side of the first singlecrystal silicon substrate, and a beam is formed. As a result, an acceleration sensor according to the first invention is produced.

In the third invention, as a first step, the main surface of a first singlecrystal silicon substrate is bonded to a second singlecrystal silicon substrate with an insulating film formed thereon, said insulating film being interposed between the first and second substrates, and as a second step, the reverse side of the first singlecrystal silicon substrate is polished to a predetermined degree, so that the first singlecrystal silicon substrate is made into a thin film. Subsequently, as a third step, a groove of a predetermined depth for formation of a beam is formed on the reverse side of the first singlecrystal silicon substrate, and as a fourth step, a film of polycrystalline silicon, an amorphous silicon or a mixture thereof is formed on the reverse side of the first singlecrystal silicon substrate, whereupon the groove is filled with the silicon film, and the surface of the silicon film is flattened. Subsequently, as a fifth step, a signal-processing circuit is formed on the first or second singlecrystal silicon substrate, whereafter the polycrystalline, amorphous or mixed silicon film is removed by etching from the reverse side of the first singlecrystal silicon substrate, and a beam is formed. As a result, an acceleration

sensor according to the first invention is produced.

BRIEF DESCRIPTION OF THE DRAWINGS

Fig. 1 is a plan of an acceleration sensor according to the first embodiment of the present invention, and Fig. 2 is a figure illustrating a section taken along the line A-A in Fig. 1.

Figs. 3 to 10 are illustrations for explanation of the manufacturing process of the first embodiment, and, respectively, sectional view for each production stage.

Fig. 11 is a plan illustrating an application example of the first embodiment, and Fig. 12 is a sectional view taken along the line B-B in Fig. 11.

Figs. 13 to 21 are illustrations for explanation of the manufacturing process of the second embodiment, and, respectively, a sectional view for each production stage.

Figs. 22 to 28 are illustrations for explanation of the manufacturing process of the third embodiment, and, respectively, a sectional view for each production stage.

Figs. 29 to 31 are illustrations for explanation of the manufacturing process of the fourth embodiment, and, respectively, a sectional view for each production stage.

Figs. 32 to 34 are illustrations for explanation of the manufacturing process examples to which the fourth embodiment is applied, and, respectively, a sectional view for each production stage.

Fig. 35 is a plan illustrating an example of a sensor tip formed by use of an acceleration sensor according to the present invention.

MOST PREFERRED EMBODIMENTS FOR WORKING THE INVENTION

In the following, the embodiments and realizations of the present invention, will be explained with reference to the attached drawings.

First Embodiment

Fig. 1 is a view plan of an acceleration sensor produced by the first embodiment of the present invention, and Fig. 2 is a sectional view taken along the line A-A in Fig. 1. In addition, in the present embodiment, the sensor part and the signal-processing circuit are formed of the same singlecrystal silicon substrate.

The present acceleration sensor is a capacity type acceleration sensor. As illustrated in Fig. 2, there is bonded onto a singlecrystal silicon substrate 8 a singlecrystal silicon substrate 1 through an SiO₂ film 9, and in the singlecrystal silicon substrate 1, there is formed a cantilever 13 by a trench 3 penetrating said substrate 1. As illustrated

in Fig. 1, this cantilever 13 has a structure such that an end side thereof is branched into two parts. The cantilever 13 can be moved in a direction parallel to the surface of the singlecrystal silicon substrate 1 (the arrow direction C in Fig. 1). In addition, in the singlecrystal silicon substrate 1, a signal-processing circuit 10 is formed and is electrically insulated from the cantilever 13 by a polysilicon film 6 and an SiO₂ film 5.

In the following, the production process of the first embodiment of the present invention, which is suitable for the production of the aforesaid structure, will be explained with reference to Figs. 3 to 10.

First, as illustrated in Fig. 3, an n-type (100) singlecrystal silicon substrate 1 with a resistance of 1 to 20 Ω ·cm is provided, and on the main surface thereof, there is formed an SiO₂ film 2 with a thickness of about 1 μ m by thermal oxidation, and the SiO₂ film 2 is formed into a predetermined pattern by a photolithographic method. This pattern is a pattern exposing, on the main surface of the silicon substrate, an area to be formed as a groove separating at least an area to be formed as a movable electrode (cantilever) from the substrate, and in the present embodiment, this pattern is formed as a pattern exposing also the main surface of the silicon substrate in an area for transversely insulating and separating the signal-processing circuit. Subsequently, on the main surface side of the singlecrystal silicon substrate 1, there is formed a trench 3 having a perpendicular wall with a predetermined depth, e.g. ranging from about 0.2 to about 30 μ m. In the present embodiment, explanation will be made with respect to the case where the wall thickness is about 3 μ m.

Subsequently, after the SiO₂ film 2 has been removed, as illustrated in Fig. 4, an n⁺ diffused layer 4 formed using phosphorus, arsenic or the like is formed on the main surface of the singlecrystal silicon substrate 1, including the internal wall of the trench 3, and further, an SiO₂ film 5 with a thickness ranging from 0.1 to 1 μ m is formed by thermal oxidation or the like. In this case, in order to prevent damage by etching, there may be conducted the so-called "sacrifice oxidation" in which SiO₂ is formed by thermal oxidation and removed before formation of the n⁺ diffused layer 4.

Subsequently, as illustrated in Fig. 5, a polysilicon film 6 is formed on the main surface of the singlecrystal silicon substrate 1, and the trench 3 is filled with the polysilicon film 6. In addition, in the case where an impurity is introduced into the polysilicon film 6 in order to use the polysilicon film 6 as a conductive path, forming a thin polysilicon layer and diffusing phosphorus or the like in a high concentration before formation of the polysilicon film 6, allows the impurity to be introduced into the

polysilicon film 6.

Next, as illustrated in Fig. 6, the surface of the polysilicon film 6 is mirror finished, so as to make the thickness of the polysilicon film 6 a predetermined value. Subsequently, boron ions or other impurity are implanted into the polysilicon film 6 to form p⁺ diffused layers 7 in predetermined areas.

On the other hand, as illustrated in Fig. 7, another (100) singlecrystal silicon substrate 8 is provided, and an SiO₂ film 9 with a thickness ranging from 0.1 to 1.0 μ m is formed on the main surface of the silicon substrate 8.

Subsequently, the singlecrystal silicon substrate 1 and the singlecrystal silicon substrate 8 are dipped into e.g. an aqueous mixed solution of aqueous hydrogen peroxide and sulfuric acid, so as to subject these substrates to a hydrophilicity-imparting treatment. Thereafter, these substrates are dried, and as illustrated in Fig. 8, the main surface of the singlecrystal silicon substrate 1 and that of the singlecrystal silicon substrate 8 are put together at room temperature, and these substrates are introduced into a furnace at 400 to 1100 °C for a period of time ranging from 0.5 to 2 hours, so as to strongly bond them.

Subsequently, as illustrated in Fig. 9, by use of an aqueous solution of an alkali type, e.g. an aqueous KOH solution or the like, the reverse side of the singlecrystal silicon substrate 1 is subjected to selective polishing. The polishing is continued until the SiO₂ film 5 is exposed. As a result, the thickness of the singlecrystal silicon substrate 1 reaches a value which is approximately determined by the depth of the trench, e.g. about 3 μ m, so that the substrate 1 is made thin.

Subsequently, as illustrated in Fig. 10, in a predetermined area of the singlecrystal silicon substrate 1, there is formed a signal-processing circuit 10 (IC circuit portion) by use of an ordinary CMOS process, bipolar process or the like. In addition, a diffused layer for connecting to wiring and a metallic electrode film composed of an aluminum film or the like are formed, and wiring at the sensor part, wiring at the circuit part, and connection of the sensor part to the circuit part are performed. In Fig. 1 and Fig. 10, a MOS transistor alone is illustrated as a part of the signal-processing circuit 10.

Further, on the upper surface of the signal-processing circuit 10, there is formed, as a passivation film 11, a plasma SiN film (P-SiN) e.g. by a plasma CD method. Subsequently, at the sensor part side, windows 12 are opened at predetermined areas of the passivation film 11, and the polysilicon film 6 filled in the trench 3 is exposed from the surface. By this window opening procedure, the singlecrystal portions where a cantilever or fixed electrodes are to be formed are demarcated from the polycrystal portions embedded in the trench,

on the surface of the substrate.

Subsequently, as illustrated in Fig. 2, by use of a 20% solution of TMAH (tetramethylammonium hydroxide) $(CH_3)_4NOH$, the polysilicon film 6 is removed by etching through the windows 12 of the passivation film 11, from the reverse side (the upper side in Fig. 2) of the singlecrystalline silicon substrate 1. In this case, the passivation film 11 (P-SiN), SiO_2 film 5, aluminum wiring layer and p^+ diffused layer (p^+ polysilicon film) 7 are hardly etched by the selective etching. Accordingly, the bonding of the singlecrystal silicon substrate to the lower singlecrystal silicon substrate 8 is secured through the p^+ diffused layer (p^+ polysilicon film) 7.

In addition, if trenches 3 are preliminarily formed also in the wide area of the cantilever 13 in Fig. 1, and etching windows 48 are provided simultaneously with the formation of the windows 12, in such a way that the etching windows 48 communicate with said trenches 3, the polysilicon film 6 below the movable part (cantilever 13) of the sensor can be more securely removed by etching through this etching window 48 when the polysilicon film 6 is removed by etching.

By the aforesaid procedures, the cantilever 13 is formed. In this case, the cantilever 13 becomes, as illustrated in Fig. 2, smaller in the thickness L_2 in a direction parallel to the surface of the singlecrystal silicon substrate 1 than in the thickness L_1 in a direction along the depth of the singlecrystal silicon substrate 1.

In a capacity type acceleration sensor, the end portions (bifurcated portions) of the cantilever 13 are formed as movable electrodes, and as illustrated in Fig. 1, the parts of the singlecrystal silicon substrate 1, opposing the end portions of the cantilever 13, are formed as fixed electrodes 14, 15, 16, and 17, respectively. In addition, as illustrated in Fig. 1, fixed electrode 14 and fixed electrode 16 are derived through an aluminium wiring layer 18a, fixed electrode 15 and fixed electrode 17 are derived through an aluminium wiring layer 18b, and the cantilever 13 (movable electrode) is derived through an aluminium wiring layer 18c. These aluminium wiring layers 18a, 18b, and 18c are connected to the signal-processing circuit 10, and by this signal-processing circuit 10, signal processing is conducted as the cantilever (movable electrode) 13 is displaced owing to an acceleration. In addition, by the n^+ diffused layers 4 (see Fig. 2) disposed on the cantilevers 13 (movable electrodes) and fixed electrodes 14, 15, 16, and 17, the electric potential is maintained at a constant value.

Although a capacity type acceleration sensor is made in the present embodiment, if a piezo resistance layer is formed at the surface of the root portion of the cantilever 13, a piezo resistance type acceleration sensor can be formed. As a matter of

course, if these two types of sensors are formed in a one and same substrate, the precision and reliability of the acceleration sensor can further be improved.

In the acceleration sensor thus produced, the singlecrystal silicon substrate 1 is bonded through an SiO_2 film to the singlecrystal silicon substrate 8, so as to form an SOI structure. In addition, in the cantilever 13, its thickness L_2 in a direction parallel to the surface of the singlecrystal silicon substrate 1 is smaller than the thickness L_1 in a direction of the depth of the singlecrystal silicon substrate 1. Accordingly, the cantilever 13 becomes movable, on the surface of the singlecrystal silicon substrate 1, in a direction parallel to the surface, whereby an acceleration to a direction parallel to the substrate surface is detected.

As mentioned in the foregoing, in the present embodiment, on the main surface of the singlecrystal silicon surface 1, there is formed a trench (groove) 3 of a predetermined depth for formation of the cantilever 13 (the first step), and the polysilicon film 6 is formed on the main surface of the singlecrystal silicon substrate 1, so as to fill the trench 3 with said polysilicon film 6, and the surface of the polysilicon film 6 is flattened (smoothed) (the second step). Subsequently, the main surface of the singlecrystal silicon substrate 1 is bonded to the singlecrystal silicon substrate 8 with an SiO_2 film 9 (insulating film) formed thereon, through said SiO_2 film 9 being interposed between the substrates 1 and 8 (the third step), whereafter the reverse side of the singlecrystal silicon substrate 1 is polished to a predetermined degree, so as to make the singlecrystal silicon substrate into a thin film (the fourth step). Subsequently, the signal-processing circuit 10 is formed on the surface of the singlecrystal silicon substrate, whereafter the polysilicon film 6 is removed by etching from the reverse side of the singlecrystal silicon substrate, so as to form the cantilever 13 (the fifth step).

Accordingly, during the process for the formation of the signal-processing circuit 10, in the course of the wafer process, the trench 3 in the surface portion of the singlecrystal silicon substrate, is filled with the polysilicon film 6, whereby contamination of the IC elements, contamination of production equipment, and degradation or deterioration of electrical properties accompanied therewith can be prevented. That is, in the wafer process, by contriving to prevent the surface structures such as concave portions or penetration holes from appearing on the wafer surface in the heat treatment, photolithographic treatment and the like, in the course of the process, it is possible to prevent contamination and the like, and to thereby stably provide acceleration sensors of high preci-

sion.

The thus produced acceleration sensor comprises the singlecrystal silicon substrate 1, which is bonded through an SiO_2 film (insulating film) to the singlecrystal silicon substrate 8, and which is made a thin film; the cantilever 13, which is formed on said singlecrystal silicon substrate 1 and which is movable in a direction parallel to the surface of the substrate; and the signal-processing circuit 10, which is also formed on the singlecrystal silicon substrate 1 and which performs signal processing as the cantilever 13 moves owing to an acceleration. When an acceleration is applied in a direction parallel to the surface of the singlecrystal silicon substrate 1, the cantilever formed on the singlecrystal silicon substrate 1 moves. As the cantilever 13 moves, signal-processing is performed by the signal-processing circuit 10 formed on the singlecrystal silicon substrate 1. In such a way as above, by a micro-machining technique using singlecrystal silicon, an acceleration sensor is formed, by the novel structure of which high precision and high reliability can be realized.

In addition, since the surface of the aforesaid cantilever 13 and the part of the singlecrystal silicon substrate 1, opposing said cantilever 13, are coated with the SiO_2 film (insulator) 5, electrode short-circuit in the capacity type acceleration sensor can previously be prevented. In addition, it suffices if at least either of the surface of the cantilever 13 or the part of the singlecrystal silicon substrate 1 opposing the cantilever 13 is coated with the SiO_2 film (insulator) 5.

Further, as an application of the present embodiment, as illustrated in Figs. 11 and 12, the cantilever may be separated from the signal-processing circuit (IC circuit portion) 10 and an air bridge wiring is formed, in order to reduce parasitic capacity. In addition, the fixed electrodes 14, 15, 16, and 17 may be formed so as to have the same structure as above. This can be realized by forming a p^+ type polysilicon film 7 at the minimum position necessary for bonding the fixed electrodes to the lower substrate.

In addition, although an aluminium wiring layer is used in the aforesaid embodiment, the wiring part may be formed by use of a polysilicon layer. Further, although two movable electrodes are formed at the end of the beam and simultaneously, four fixed electrodes 14, 15, 16, and 17 are formed, in the aforesaid embodiment, the movable and fixed electrodes may be formed like the teeth of a comb in order to further improve the sensitivity of the sensor.

In addition, an oxide film may selectively be formed, instead of the formation of the p^+ polysilicon film 7.

Second Embodiment

Next, there will be made explanations about the production process in the second embodiment, laying stress on the points different from those in the first embodiment. In addition, in the second embodiment to be hereafter explained, explanations will be made by way of example of the case where a sensor having a structure according to the structure illustrated in Figs. 1 and 2 as explained in the aforesaid first embodiment, and there will be illustrated a sectional view corresponding to the A-A section of Fig. 1.

In the aforesaid first embodiment, in order to form the cantilever 13, the p^+ diffused layer (p^+ polysilicon film) 7 is formed for the purpose of separating the cantilever portion from the singlecrystal silicon substrate at a predetermined distance, but in the present embodiment, a concave portion is formed before formation of a trench, for the purpose of separating the cantilever from the substrate at a predetermined distance.

In Figs. 13 to 21, the production process is illustrated.

First, as illustrated in Fig. 13, an n type (100) singlecrystal silicon substrate 20 is provided, and on the main surface of the provided singlecrystal silicon substrate 20, there is formed a concave portion 21 with a predetermined depth e.g. ranging from 0.1 to 5 μm . Subsequently, as illustrated in Fig. 14, on the main surface of the singlecrystal silicon substrate 20, there is formed an SiO_2 film 22, and a pattern is formed by a photolithographic means, in the same way as in the aforesaid first embodiment. Subsequently, on the main surface of the singlecrystal silicon substrate 20 including the bottom of the concave portion 21, there is formed a trench with a depth ranging from about 0.1 to about 30 μm (3 μm in the present embodiment) by dry etching or the like.

Subsequently, as illustrated in Fig. 15, on the main surface of the singlecrystal silicon substrate 20 including the internal wall of the trench 23, there is formed an n^+ diffused layer 24, and an SiO_2 film 25 is formed by thermal oxidation. Thereafter, as illustrated in Fig. 16, a polysilicon film 26 is deposited in the trench 23 by the LPCVD method.

Subsequently, as illustrated in Fig. 17, the surface of the polysilicon film 26 is polished by use of the SiO_2 film as an etching stopper, so as to smooth the surface. In the above case, although it is desirable that the surfaces of the polysilicon film 26 and the SiO_2 film 25 become smooth, even if the polysilicon film 26 is rather indented, so long as the surface of the SiO_2 film is made smooth, no inconvenience is caused in the subsequent wafer cementing.

On the other hand, as illustrated in Fig. 18, another (100) singlecrystal silicon substrate 27 is provided, and, on the main surface of the substrate 27, there is formed an SiO₂ film with a thickness ranging from 0.1 to 1.0 μm by thermal oxidation of the substrate. Subsequently, singlecrystal silicon substrates 20 and 27 are dipped in e.g. a solution of an aqueous hydrogen peroxide and sulfuric acid, so as to subject them to a hydrophilicity-imparting treatment. Subsequently, the substrates are dried, and thereafter, the main surfaces of the two singlecrystal silicon substrates 20 and 27 are put together at room temperature, and introduced into a furnace at 400 to 1100°C for a period of time ranging from 0.5 and 2 hours, so as to strongly bond the two surfaces.

Subsequently, as illustrated in Fig. 19, the reverse side of the singlecrystal silicon substrate 20 is subjected to selective polishing by use of an aqueous solution of alkali type, e.g. an aqueous KOH solution. The selective polishing is performed until the SiO₂ film 25 appears on the surface. As a result, the thickness of the singlecrystal silicon substrate 20 becomes e.g. about 3 μm, so as to be made a thin film.

Subsequently, as illustrated in Fig. 20, a signal-processing circuit (IC circuit portion) 10 is formed through an ordinary CMOS process, bipolar process, or the like. Further, on the upper surface of the signal-processing circuit 10, there is formed, as a passivation film 11, a plasma SiN film (P-SiN film) by e.g. plasma CVD method. Subsequently, windows 12 are opened at predetermined areas of the passivation film 11, and the polysilicon film 20 is exposed to the surface at the sensor portion.

Subsequently, as illustrated in Fig. 21, by use of a 20% solution of TMAH (tetramethylammonium hydroxide) (CH₃)₄NOH, the polysilicon film 26 is removed by etching from the reverse side of the singlecrystal silicon substrate 20 through the windows 12 on the passivation film 11. In the above case, the passivation film 11 (P-SiN), SiO₂ film, and aluminium wiring layer are hardly etched by the selective etching.

As a result, a cantilever 13 is formed.

Also by the present embodiment, there is obtained the same effect as in the aforesaid first embodiment.

Third Embodiment

Next, there will be made explanations about the production process in the third embodiment, laying stress on the differential points between the first and third embodiments.

Although, in the aforesaid first and second embodiments, the trench is filled with polysilicon before the bonding of the wafers, in the present

embodiment, the trench is filled with polysilicon after the bonding of wafers, and in the final stage, the thus filled polysilicon is removed, so as to produce an acceleration sensor.

In Figs. 22 to 28, the production process is illustrated.

First, as illustrated in Fig. 22, an n-type (100) singlecrystal silicon substrate 30 is provided, and on the main surface of the provided singlecrystal silicon substrate 30, there is formed a concave portion 31 in a depth ranging from 0.1 to 5 μm, in the same way as in the aforesaid second embodiment. On the other hand, as illustrated in Fig. 23, a singlecrystal silicon substrate 32 is provided, and an SiO₂ film is formed by thermal oxidation on the main surface of the singlecrystal silicon substrate 31. Thereafter, the main surface of the singlecrystal silicon substrate 30 is bonded to the main surface of a single crystal silicon substrate 32.

Subsequently, as illustrated in Fig. 24, the reverse side of the singlecrystal silicon substrate 30 is subjected to mirror polishing to a predetermined thickness (0.1 to 30 μm). Thereafter, as illustrated in Fig. 25, there is formed an SiO₂ film 34 to a thickness ranging from 0.1 to 2 μm, following which the SiO₂ film is subjected to patterning, and a trench 35 is formed by etching. Thereby, a cantilever 13 and a transversal insulatedly separated area of the processing circuit portion are formed.

Next, by thermal diffusion or the like, there is introduced an N type impurity of arsenic or phosphorus in a high concentration, and a highly concentrated n⁺ layer 36 is formed in the silicon area which is not covered with SiO₂ films 33 and 34.

Subsequently, as illustrated in Fig. 26, a thermal oxidation film is formed on the side wall of the trench 35 and the like, whereafter a polysilicon film 37 is formed on the surface of the singlecrystal silicon substrate 30, and the trench 35 is filled with the polysilicon film 37. Thereafter, as illustrated in Fig. 27, the surface of the polysilicon film 37 is selectively polished and smoothed until the SiO₂ film 34 appears on the surface. Further, as illustrated in Fig. 28, a signal-processing circuit 10 is formed, and finally, the polysilicon film 37 is removed by etching from the reverse side (upper surface side) of the singlecrystal silicon substrate 30, so as to again separate the cantilever 13 from the substrate to allow it to move.

As described above, in the present third embodiment, the main surface of the singlecrystal silicon substrate 30 is bonded to the singlecrystal silicon substrate 32 with the SiO₂ film (insulating film) 33 formed thereon, through said SiO₂ film 33 being interposed between the substrates 30 and 32 (first step), and the reverse side of the singlecrystal silicon substrate is polished to a predetermined degree, so as to make the singlecrystal silicon

substrate 30 a thin film (second step). Subsequently, on the reverse side of the singlecrystal silicon substrate 30, there is formed a trench (groove) 35 with a predetermined depth for formation of a cantilever 13 (third step), and the trench 35 is filled with the polysilicon film 37, and the surface of the polysilicon film 37 is smoothed (fourth step). Subsequently, a signal-processing circuit is formed on the singlecrystal silicon substrate 30, whereafter the polysilicon film 37 is removed, by etching, from the reverse side of the singlecrystal silicon substrate 30, so as to form a cantilever 13 (fifth step).

Therefore, in the process of formation of the signal-processing circuit 10 in the wafer, the trench 35 is filled with the polysilicon film 37 in the upper surface part of the singlecrystal silicon substrate 30, whereby contamination of the IC elements, contamination of the production apparatus, and degradation or deterioration of electrical properties attended therewith can be prevented. That is, by contriving not to make a surface structure such as a concave portion or a perforation of the like appear on the wafer surface in the heat treatment, the photolithographical treatment or the like in the course of the wafer process, contamination and the like can be prevented, so as to stabilize the wafer process, and a stable supply of acceleration sensors, of high precision, can be produced.

Fourth Embodiment

In the following, there will be made explanations about the production process of the fourth embodiment, laying stress on the differences between the present embodiment and the third embodiment.

The present embodiment is intended to produce an acceleration sensor at a lower cost than the production process of the third embodiment.

In Figs. 29 to 31, the production process is illustrated.

First, as illustrated in Fig. 29, an SiO₂ film with a thickness ranging from 0.1 to 2 μ m is formed on the main surface of a singlecrystal silicon substrate 40, and a singlecrystal silicon substrate 42 is bonded to the substrate 40 so as to interpose the SiO₂ film 41 between the substrates 40 and 42. Subsequently, as illustrated in Fig. 30, the upper surface of the singlecrystal silicon substrate 42 is polished so as to make the thickness of the singlecrystal silicon substrate a predetermined value. That is, the thickness of the singlecrystal silicon substrate 42 is reduced to e.g. about 3 μ m. Thereafter, a highly concentrated n⁺ diffused layer 43 is formed on the upper surface of the singlecrystal silicon substrate 42, and further, an SiO₂ film 44 is formed thereon. It suffices if this highly concentrated n⁺ diffused layer 43 is formed corresponding to the

parts of the sensor which will be formed as movable electrodes and fixed electrodes.

Subsequently, as illustrated in Fig. 31, patterning is applied to an SiO₂ film, as in the third embodiment, and a trench 45 is formed on the singlecrystal silicon substrate 42. Thereafter, the SiO₂ film 41 below this trench 45 is partly removed by etching with an aqueous hydrofluoric acid solution. In this case, a part of SiO₂ film 41, below the part to be formed as a cantilever 13, is completely removed, and another part of the SiO₂ film 41, below the part to be formed as solid electrodes and signal-processing circuit portion, is left. Because the lower portion of the part is to be formed as the cantilever 13 it is narrower than with the other part. In addition, in the above case, the highly concentrated n⁺ diffused layer 43 is separated into the cantilever 13 and fixed electrodes.

Subsequently, through the same processes as illustrated in Figs. 26 to 28, there is produced a capacity type acceleration sensor.

In the following, there will be explained application examples of the fourth embodiment with reference to Figs. 32 to 34.

First, as illustrated in Fig. 32, an SiO₂ film with a thickness ranging from 0.1 to 2 μ m is formed on the main surface of the singlecrystal silicon substrate 40, and a concave portion 47 with a depth ranging from 0.1 to 3 μ m is formed at the area of the main surface of the singlecrystal silicon substrate 42, on which area a cantilever is to be formed. Subsequently, the main surface of the singlecrystal silicon substrate 42 is bonded to the main surface of the singlecrystal silicon substrate 40, the SiO₂ film 41 being put therebetween. Further, as illustrated in Fig. 33, the upper surface of the singlecrystal silicon substrate 42 is polished so as to give the singlecrystal silicon substrate 42 a predetermined thickness. That is, the thickness of the singlecrystal silicon substrate 42 is made thin to a value of about 3 μ m. Subsequently, the aforesaid highly concentrated diffused layer 43 is formed on the upper surface of the singlecrystal silicon substrate 42, and an SiO₂ film 44 is formed thereon.

Subsequently, as illustrated in Fig. 34, onto the singlecrystal silicon substrate 42, there are formed trenches 45 extending to the concave portions 47, and cantilevers 13 are formed.

Thereafter, a capacity type acceleration sensor is produced through the same processes as illustrated in Figs. 26 to 28.

By conducting the aforesaid procedures, electrical insulation can be made more securely as compared with the case where the SiO₂ film 41 is partly removed by etching. In addition, the mechanical strength of the sensor can be improved.

In addition, the present invention is not restricted to the aforesaid embodiments, and is applicable to a twin-lever spring or a polyever spring embodiment, in addition to a cantilever spring embodiment.

In addition, as illustrated in Fig. 35, it is possible to form two acceleration sensors 13a and 13b onto a singlecrystal silicon substrate 50, for detecting the acceleration in the direction X by the acceleration sensor 13a, and the acceleration in the direction Y by the acceleration sensor 13b. Further, it is possible to form an acceleration sensor capable of detecting the acceleration in a direction surface perpendicular to these X and Y direction acceleration sensors 13a and 13b, on the same substrate, so as to detect an acceleration in three-dimensionals. In addition, when the present acceleration sensor is used as a capacity type acceleration sensor, it is possible to further stabilize the properties by forming the present acceleration sensor into a so-called "servo type" sensor (with a closed-loop circuit).

In addition, in the aforesaid embodiments, the trenches (grooves) 3, 23, and 35 are filled with polysilicon films 6, 26, and 37, respectively, but there may be used a film of polysilicon, amorphous silicon or a mixed silicon containing polysilicon and amorphous silicon.

In addition, in the aforesaid embodiments, a sensor portion and a signal-processing portion are formed in the singlecrystal silicon substrate to be formed as the upper side, but the present acceleration sensor is not restricted to such a structure, and it is possible to utilize also a singlecrystal silicon substrate formed as a base, and form a sensor portion and a signal-processing portion on the lower substrate.

As described in detail in the foregoing, according to the present invention, high precision and high reliability can be realized by formatting a novel structure. In addition, when a signal-processing circuit is provided on the same chip as a movable beam, since there is produced neither a hollow part nor a groove during the production process, it is possible to make the processing stable. In addition, it is at the final step that the movable beam is made movable with respect to the substrate, whereby, in the case of the movable beam being bonded to the lower substrate to be formed as a pedestal or in the case of a circuit being formed, or the like, minute beams can be prevented from being broken, and the yield thereof can be made higher. In addition, since it is a micro-machining technique which determines the shape of the present acceleration sensor, the present acceleration sensor can be produced with high precision.

[Industrial Availability]

As described in the foregoing, the present invention is useful for the production of a semiconductor acceleration sensor having minute movable parts, and the present acceleration sensor is suitable as an acceleration sensor to be used for air bag system, suspension control system and the like of automobiles. In addition, the present invention can be applied to a capacity type acceleration sensor for detecting acceleration in multiple directions.

Claims

1. An acceleration sensor, characterized in that it comprises:
 - a second singlecrystal silicon substrate, which is bonded onto a first singlecrystal silicon substrate, an insulating film being interposed between the substrates;
 - a movable beam, formed on at least one of said first or second singlecrystal silicon substrate, and which is movable in a direction parallel to the surface of the substrate; and
 - a signal-processing circuit, formed on at least one of the said first or second singlecrystal silicon substrate for effecting signal processing as said beam moves owing to an acceleration.
2. An acceleration sensor as claimed in claim 1, wherein said beam is smaller in thickness in a direction parallel to the surface of said singlecrystal silicon substrates as compared to the thickness in a direction of the depth of said singlecrystal silicon substrates.
3. An acceleration sensor as claimed in claim 1, wherein at least one of the surface of said beam and the surface of second singlecrystal silicon substrate opposing said beam is covered with an insulator.
4. A process for producing an acceleration sensor, comprising:
 - a first step of forming, on a main surface of a first singlecrystal silicon substrate, a groove of a predetermined depth at an area surrounding a beam to be formed;
 - a second step of depositing, on the main surface of said first singlecrystal silicon substrate, a film of a polycrystalline silicon, amorphous silicon or mixture thereof, so as to fill said groove with said silicon film, and smoothing the surface of said silicon film;
 - a third step of bonding the main surface of said first singlecrystal silicon substrate to the

second singlecrystal silicon substrate with an insulating film interposed therebetween;

a fourth step of polishing a surface of said first singlecrystal silicon substrate on the side opposite to the surface thereof bonded to the second singlecrystal silicon substrate to a predetermined degree, so as to make the first singlecrystal silicon substrate a thin film; and

a fifth step of exposing said film of polycrystalline silicon, amorphous silicon or a mixture thereof on said polished surface of the first singlecrystal silicon substrate at an area corresponding to the position where said groove is formed, and removing said silicon film by etching from said exposed area, so as to make the beam movable.

5. A process for producing an acceleration sensor as claimed in claim 4, wherein, in said first step, said predetermined depth is set according to the thickness of said beam in the vertical direction thereof. 20
6. A process for producing an acceleration sensor as claimed in claim 4, wherein, in said third step, said insulating film is formed on the surface of said second singlecrystal silicon substrate. 25
7. A process for producing an acceleration sensor as claimed in claim 4, wherein, in said second step, there remains said flat silicon film on the main surface of said first singlecrystal silicon substrate. 30
8. A process for producing an acceleration sensor as claimed in claim 7, wherein, prior the said third step, there is added a step of making said silicon film remaining on the main surface of said singlecrystal silicon substrate to be resistant to the etching in said fifth step, except for the silicon film positioned at an area surrounding said movable beam. 40
9. A process for producing an acceleration sensor as claimed in claim 4, wherein said first step additionally includes a step of forming a concave portion on the main surface of said first singlecrystal silicon substrate, at the position where said beam is to be formed. 45
10. A process for producing an acceleration sensor as claimed in claim 4, wherein, prior to said fifth step, there is added a step of forming a semi-conductor element on said first or second singlecrystal silicon substrate. 55

11. A process for producing an acceleration sensor, comprising:

a first step of bonding the main surface of a first singlecrystal silicon substrate to a second singlecrystal silicon substrate with an insulating film interposed therebetween;

a second step of polishing a surface of said first singlecrystal silicon substrate opposite to the bonded surface of the singlecrystal silicon substrate to a predetermined degree, so as to make the first singlecrystal silicon substrate a thin film;

a third step of forming a groove in the first singlecrystal substrate, the groove extending from the polished surface side of the substrate to said insulating film in an area surrounding a movable beam to be formed;

a fourth step of depositing, from the polished surface side of the said first singlecrystal silicon substrate, a film of a polycrystalline silicon, amorphous silicon, or mixture thereof, so as to fill said groove with said silicon film, and smoothing the surface of said silicon film; and

a fifth step of forming a semiconductor element on said first or second singlecrystal silicon substrate, and thereafter removing by etching said silicon film from said polished surface side of said first singlecrystal silicon substrate, so as to make the beam movable.

12. A process for producing an acceleration sensor as claimed in claim 11, wherein, in said first step, said insulating film is formed on the surface of said second singlecrystal silicon substrate. 35
13. A process for producing an acceleration sensor as claimed in claim 11, wherein said fifth step includes a step of removing said insulating film at a position corresponding to the position where said beam is formed. 40
14. A process for producing an acceleration sensor as claimed in claim 11, wherein said first step includes a step of forming, prior to said bonding, a concave portion in an area of the main surface of said first singlecrystal silicon substrate, corresponding to the position where said beam is to be formed. 45

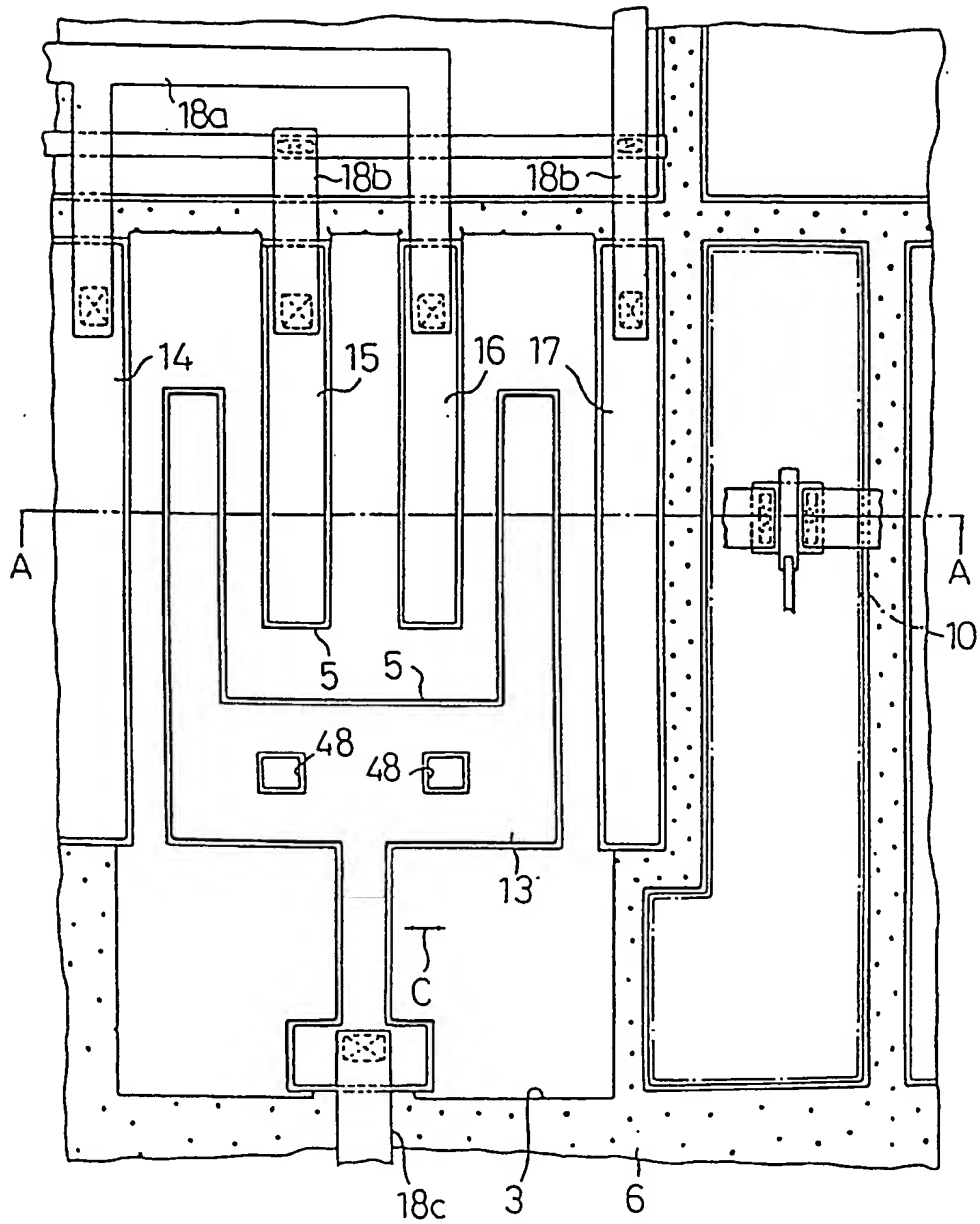


Fig. 1

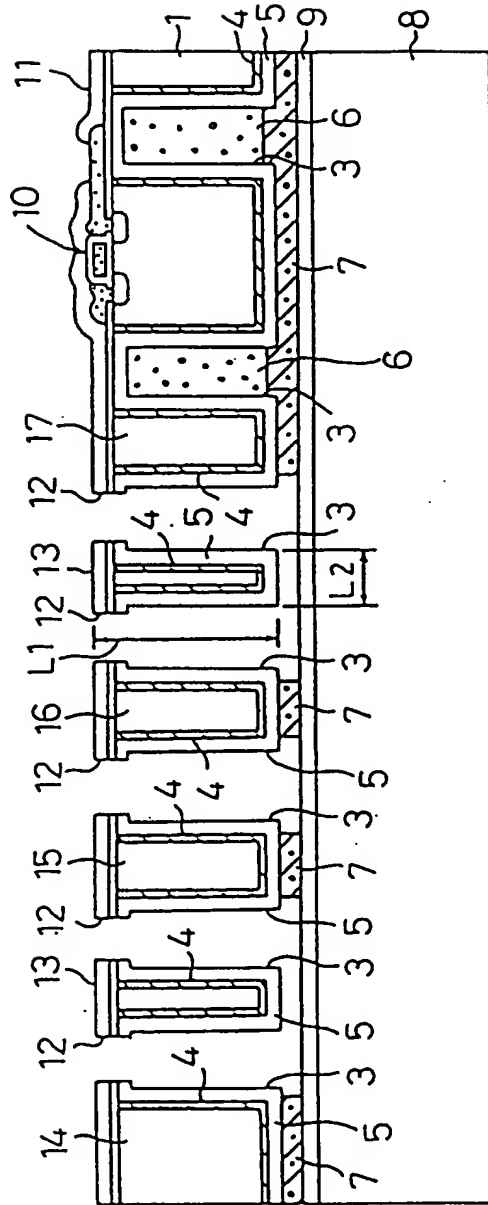


Fig. 2

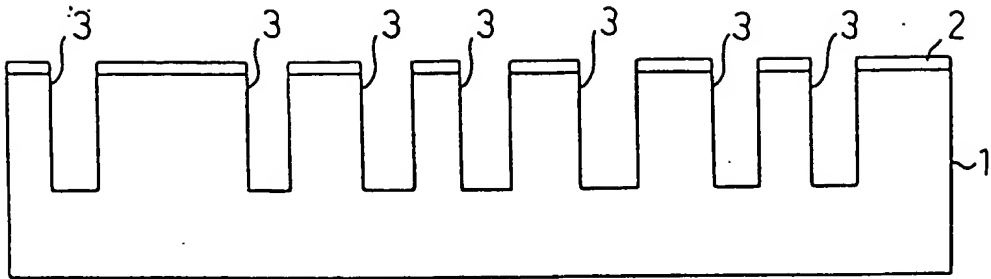


Fig. 3

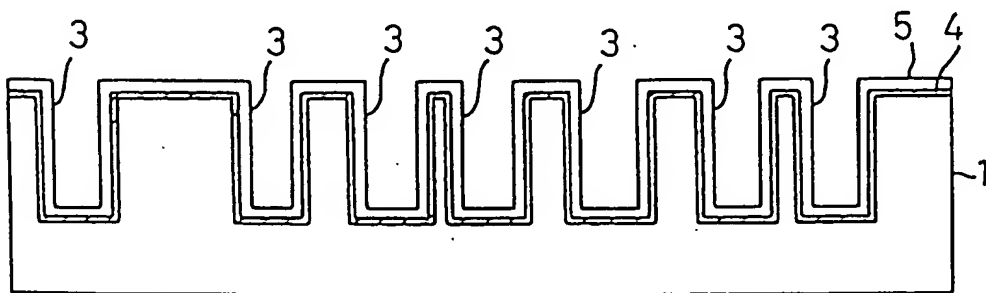


Fig. 4

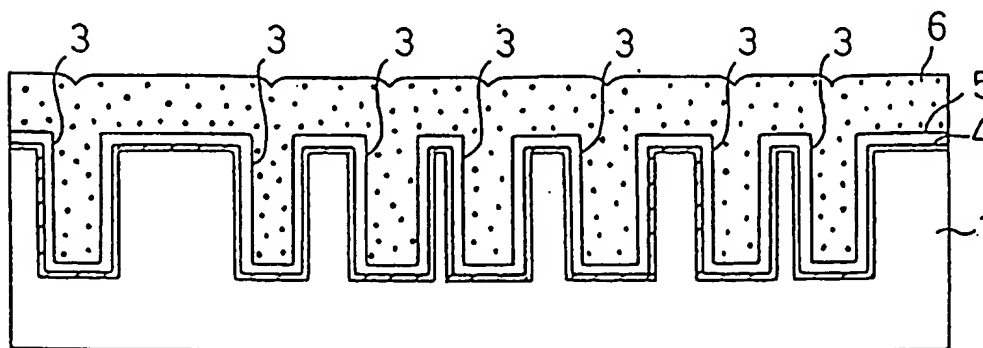


Fig. 5

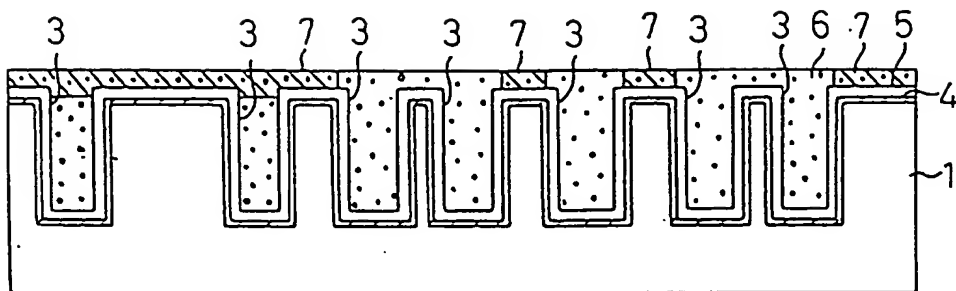


Fig. 6

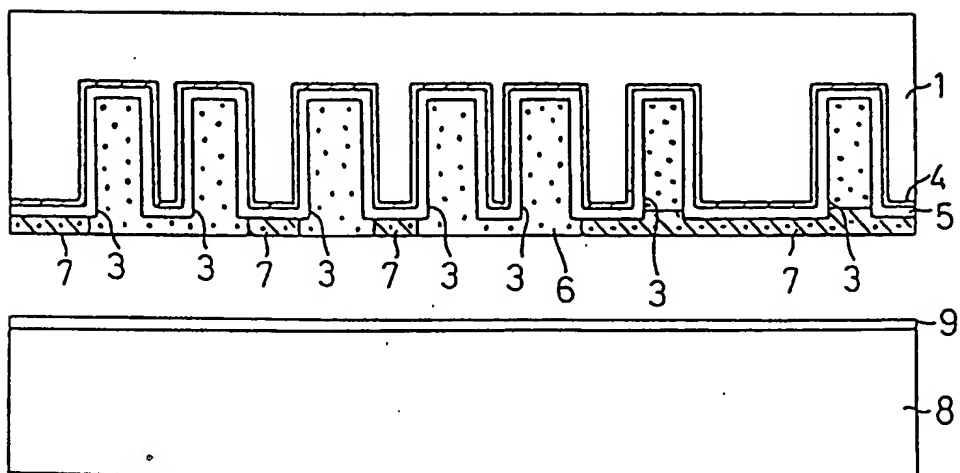


Fig. 7

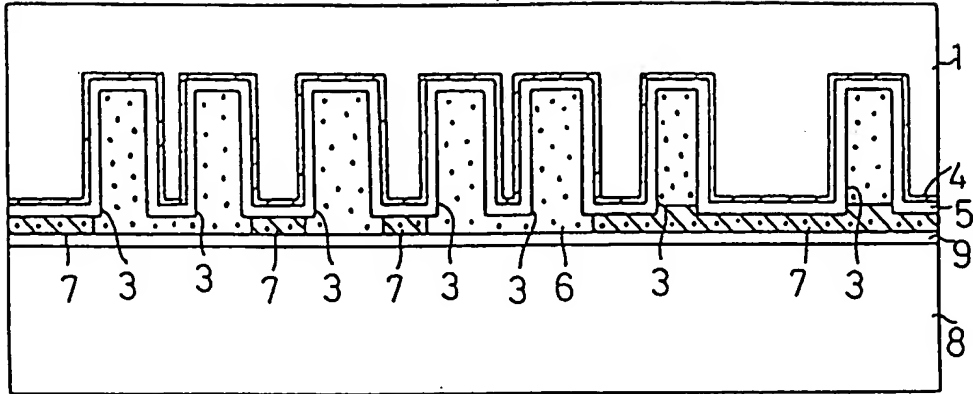


Fig. 8

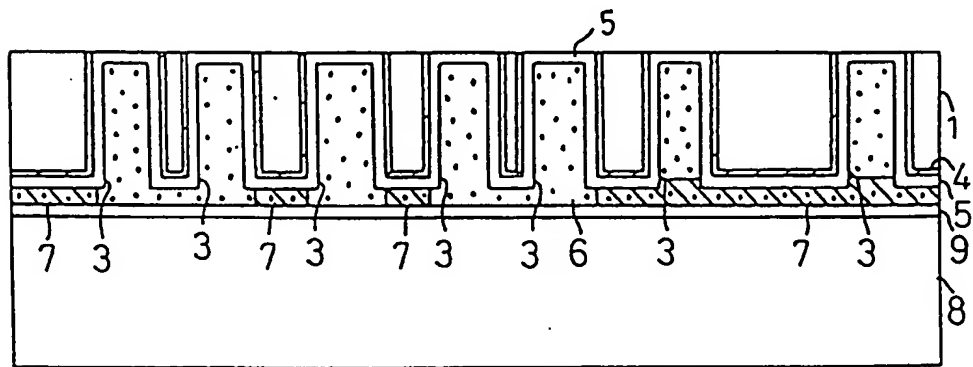


Fig. 9

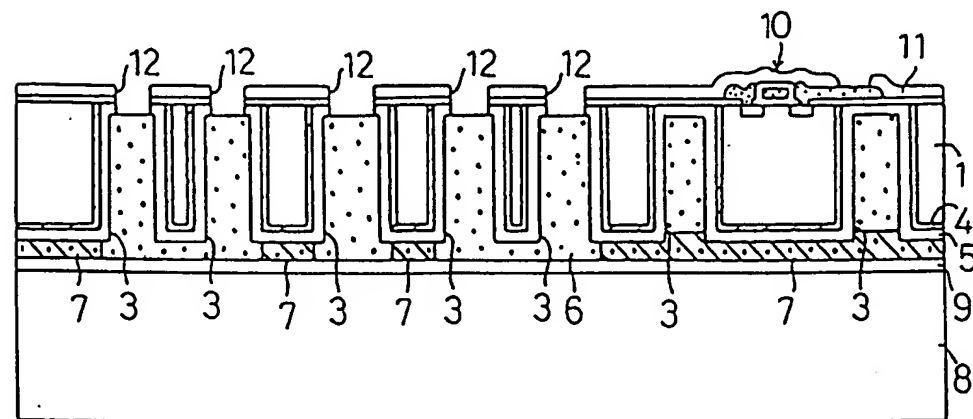


Fig. 10

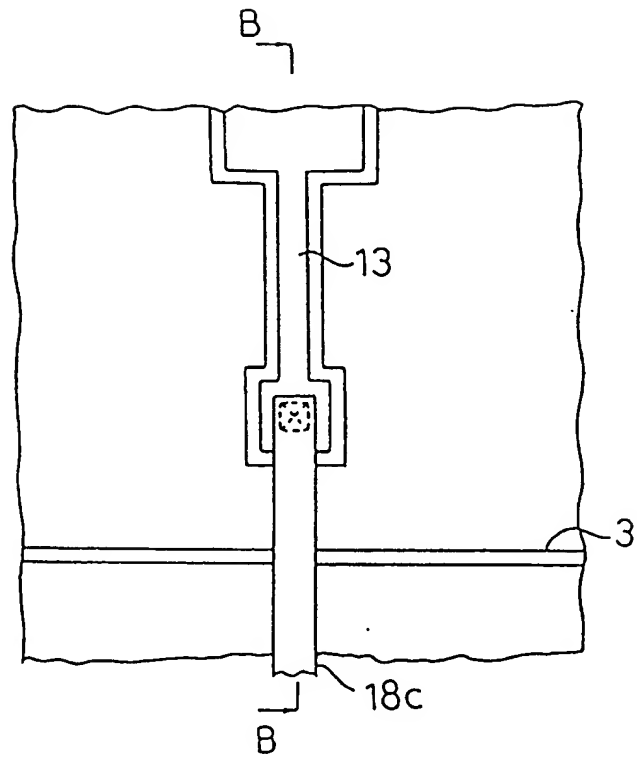


Fig. 11

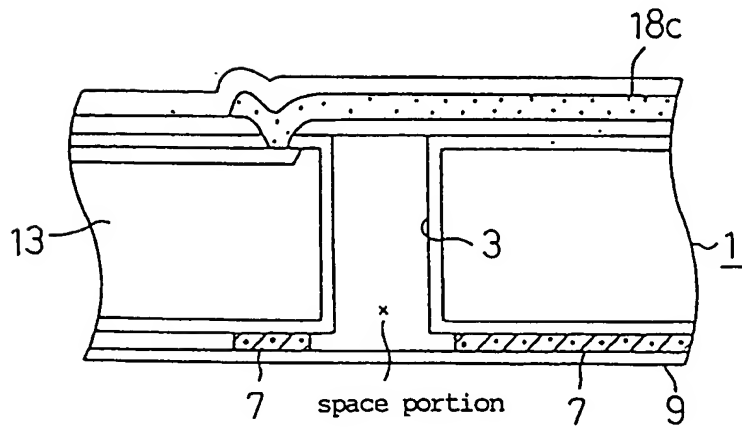


Fig. 12

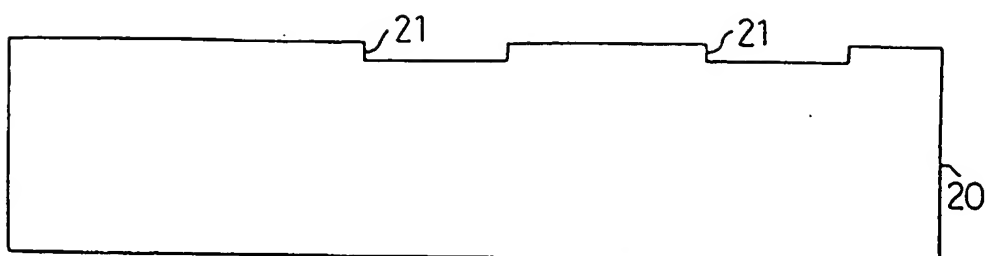


Fig. 1.3

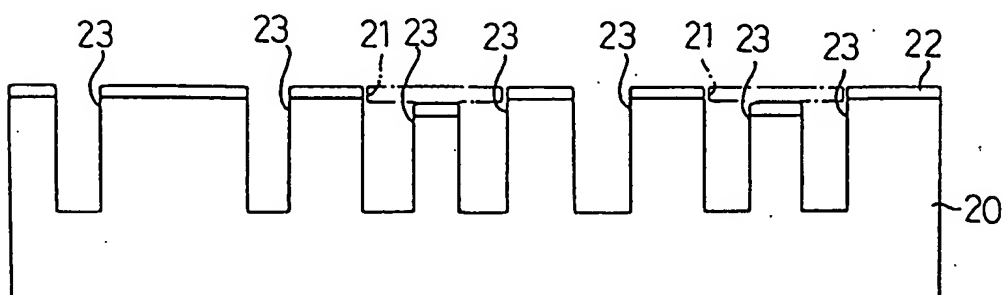


Fig. 1.4

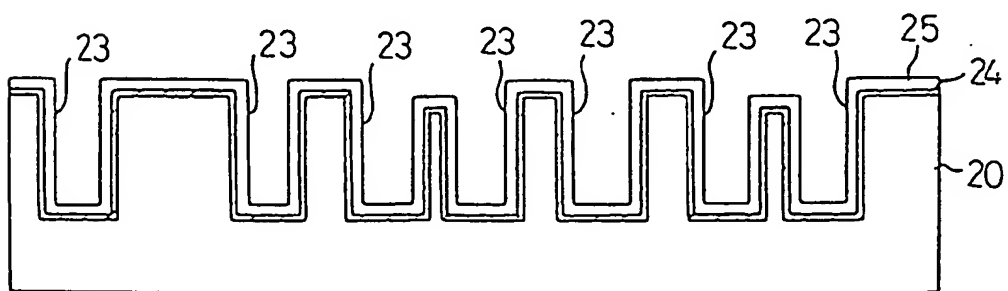


Fig. 1.5

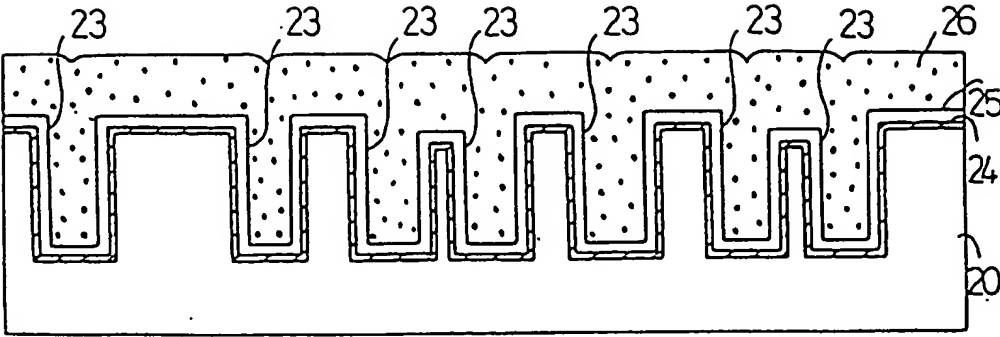


Fig. 16

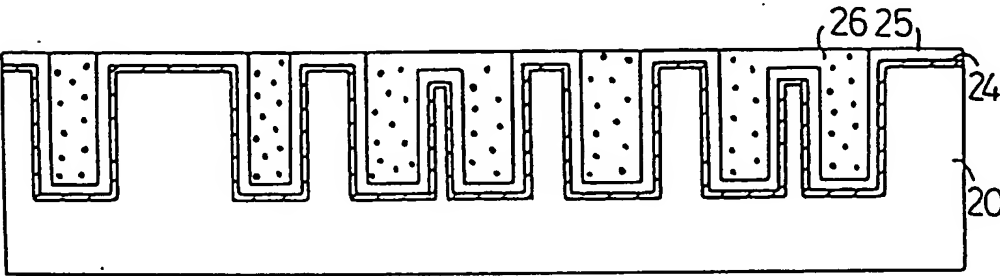


Fig. 17

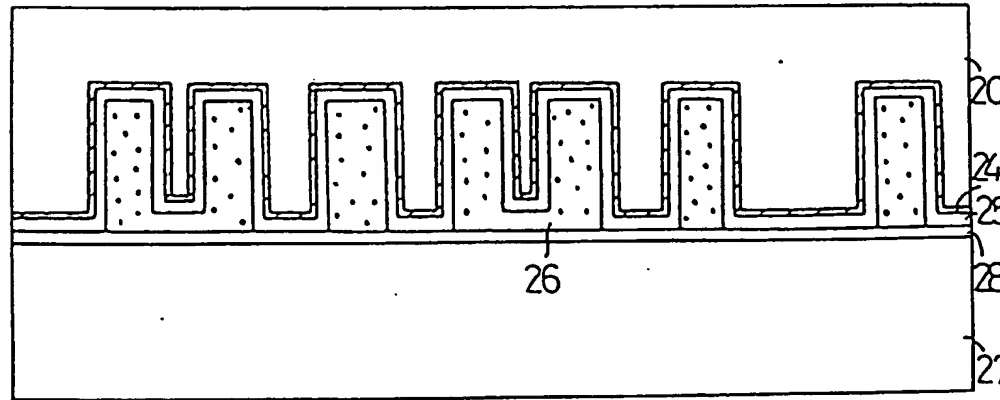


Fig. 18

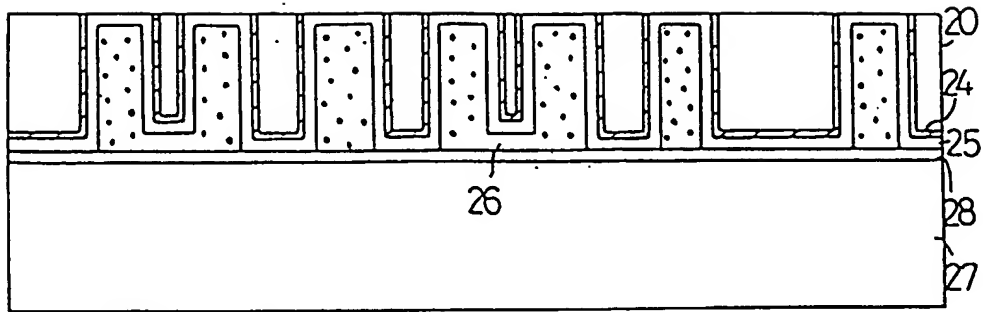


Fig. 19

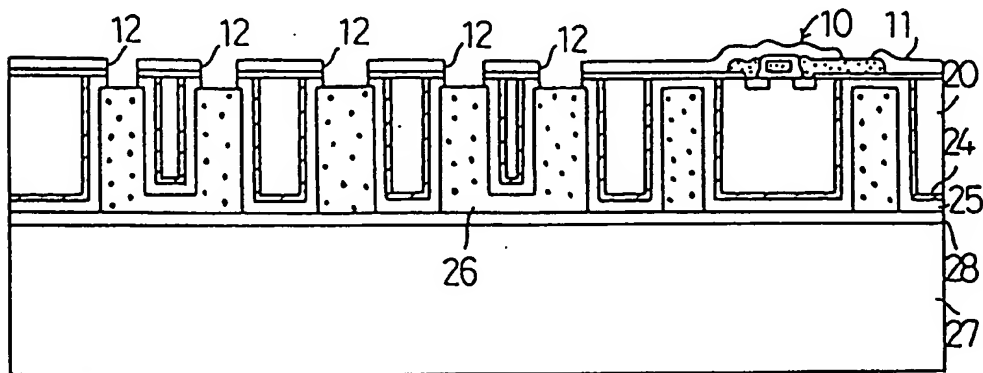


Fig. 20

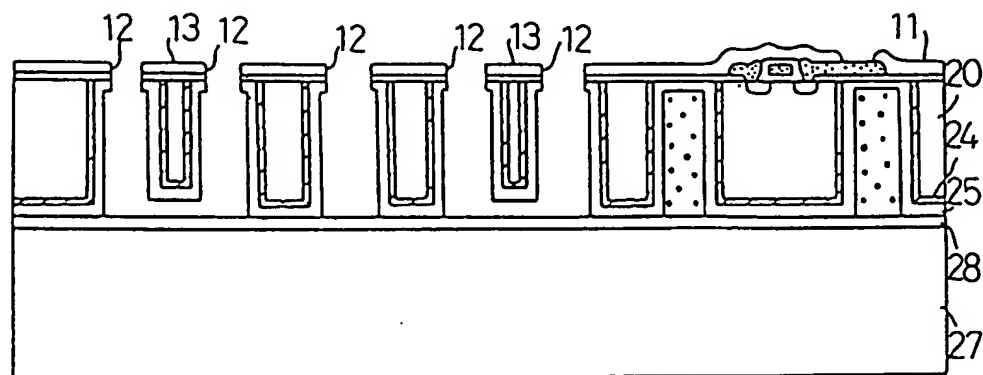


Fig. 21

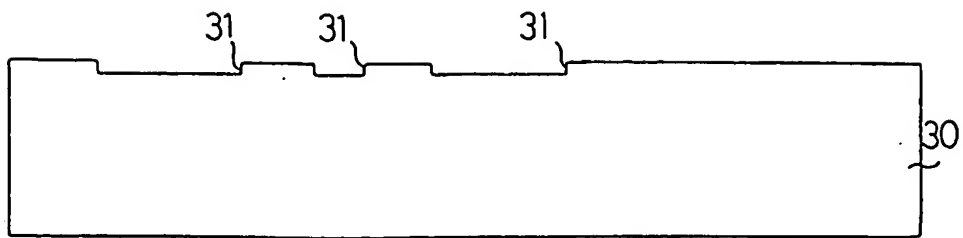


Fig. 22

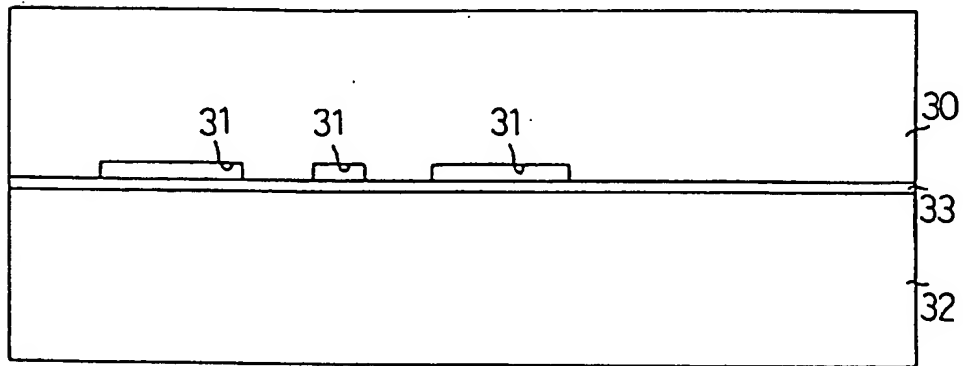


Fig. 23

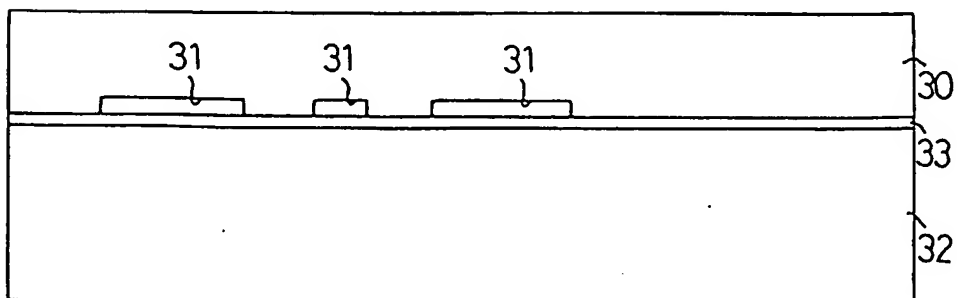


Fig. 24

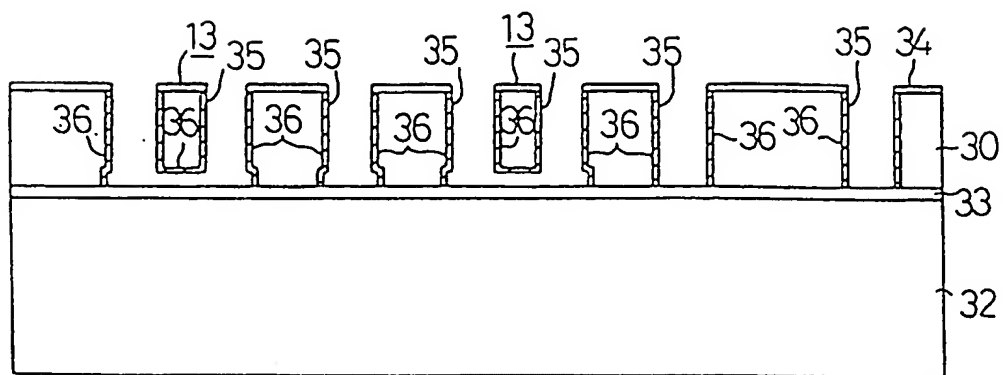


Fig. 25

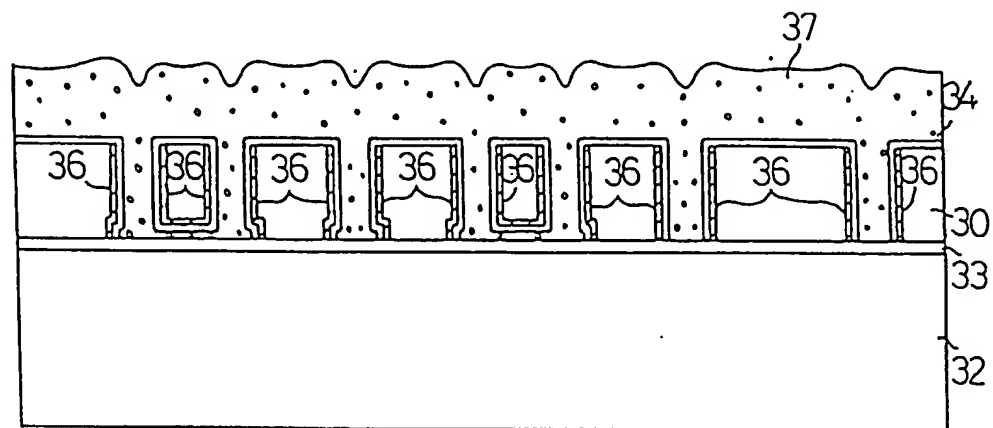


Fig. 26

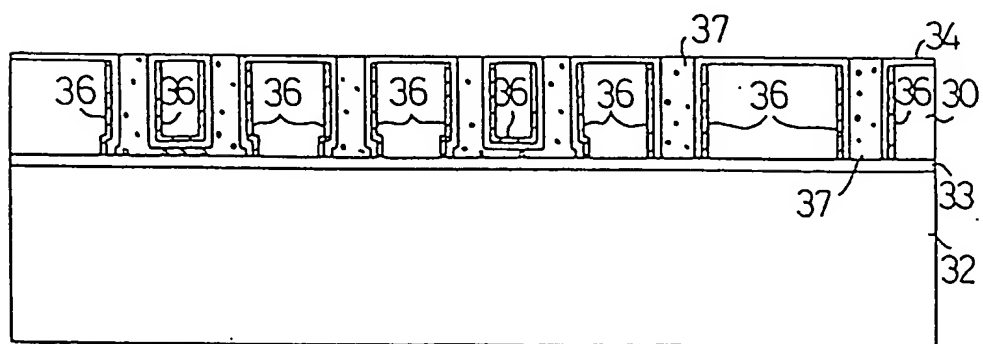


Fig. 27

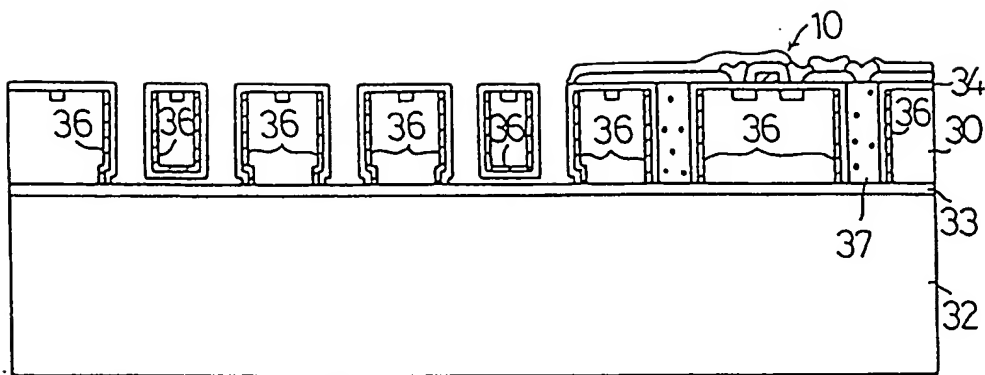


Fig. 28

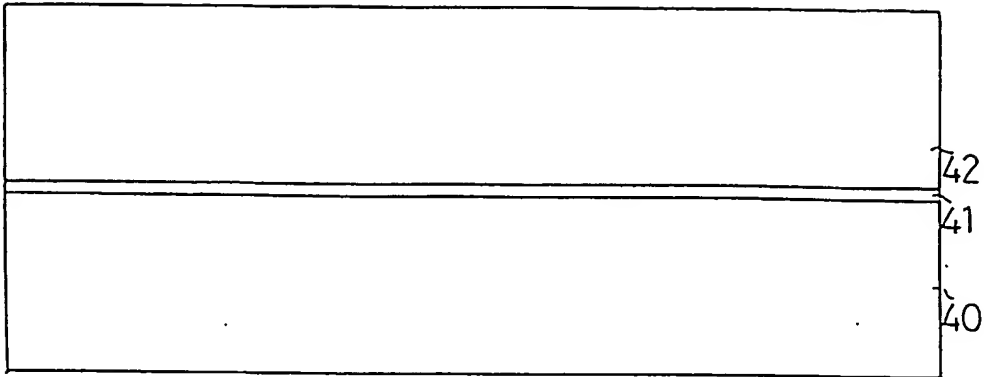


Fig. 29

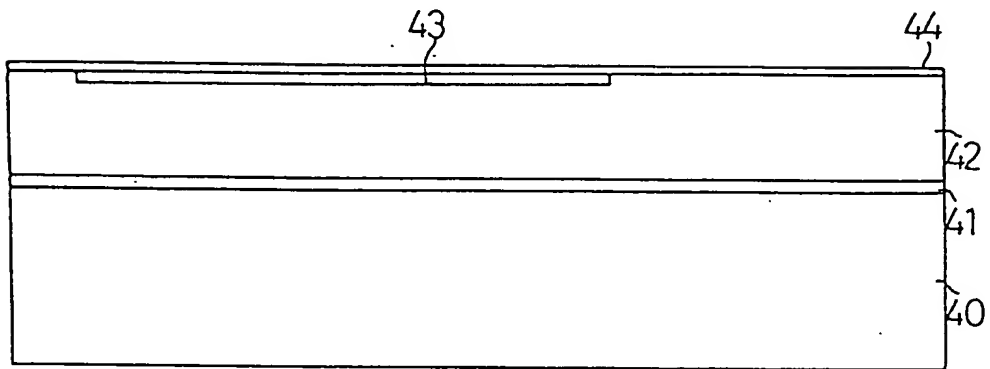


Fig. 30

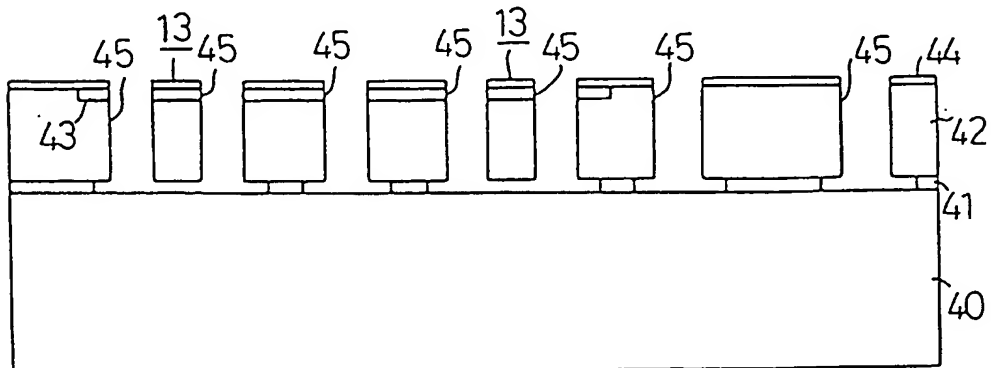


Fig. 31

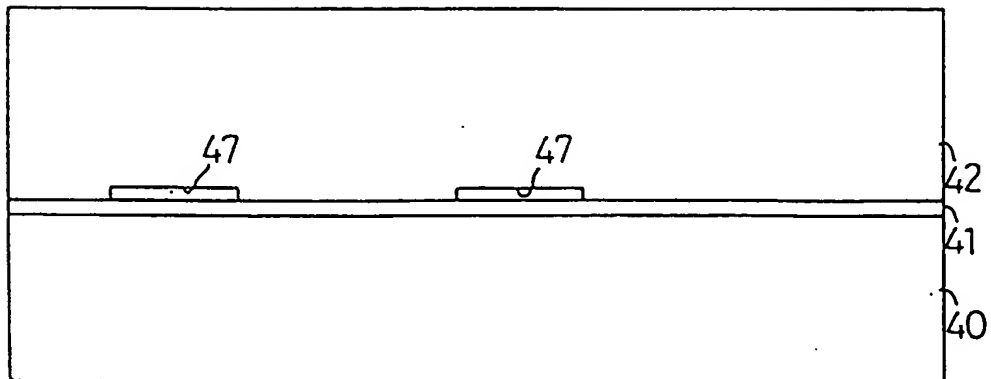


Fig. 32

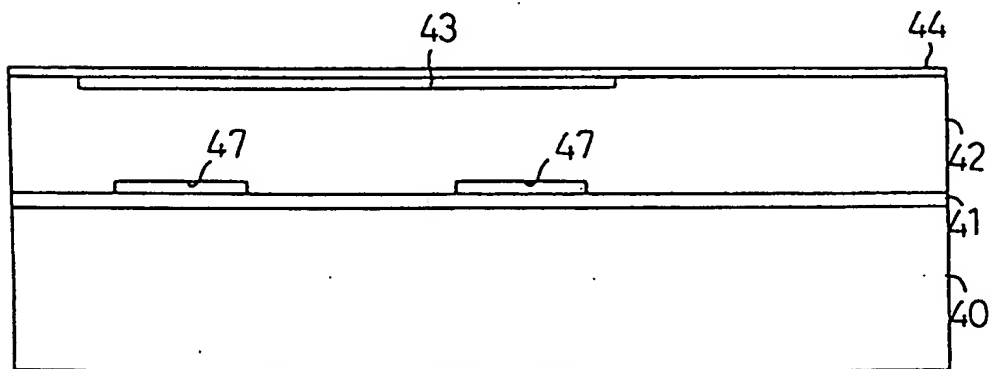


Fig. 33

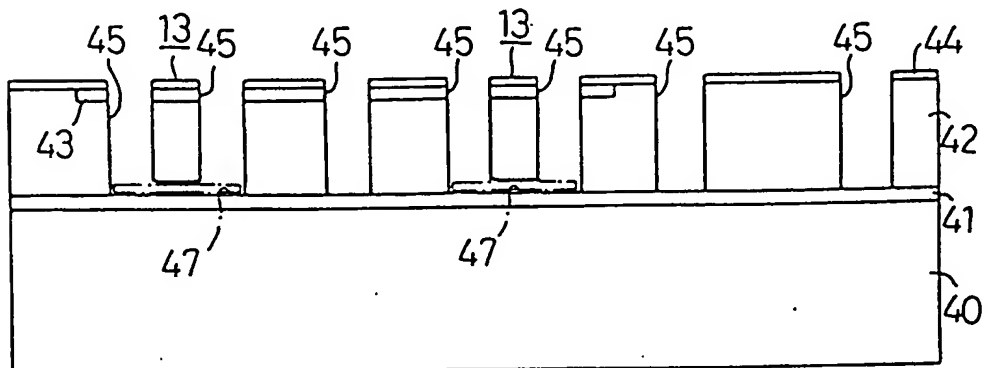


Fig. 34

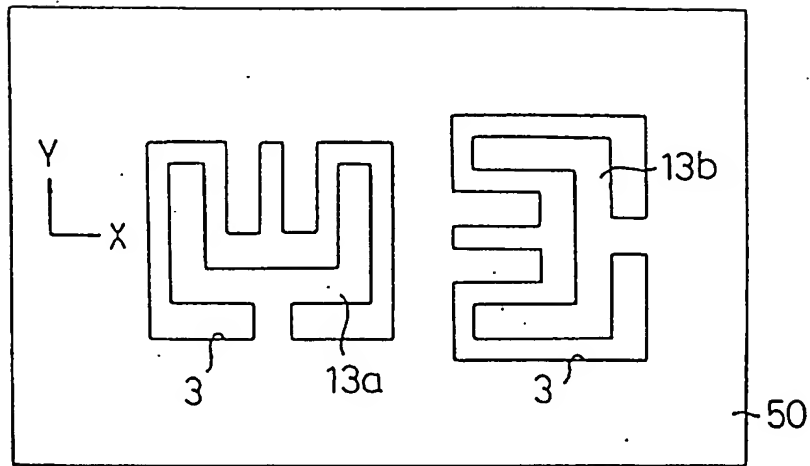


Fig. 35

INTERNATIONAL SEARCH REPORT

International application No.

PCT/JP93/00535

A. CLASSIFICATION OF SUBJECT MATTER

Int. Cl⁵ G01P15/125

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

Int. Cl⁵ G01P15/125, G01P15/08

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Jitsuyo Shinan Koho 1971 - 1993

Kokai Jitsuyo Shinan Koho 1971 - 1993

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	JP, A, 60-244864 (Becton Dickinson and Co.), December 4, 1985 (04. 12. 85), & US, A, 4,574,327 & US, A, 4,609,968 & DB, B2, 2,158,945 & DE, C2, 3,507,820 & FR, B1, 2,564,593	1-3
A	JP, A, 62-207917 (Fujitsu Ltd.), September 12, 1987 (12. 09. 87), & FR, A1, 2,585,474 & DE, A1, 3,621,585 & DB, A1, 2,178,856	1-3
A	JP, A, 62-27666 (Litton System Inc.), February 5, 1987 (05. 02. 87), & US, A, 4,679,434 & US, A, 4,744,249 & US, A, 4,744,248	4-14
A	JP, A, 61-73071 (International Standard Electric Corp.), April 15, 1986 (15. 04. 86), (Family: none)	4-14

☒ Further documents are listed in the continuation of Box C.
 ☐ See patent family annex.

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"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone

"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art

"A" document member of the same patent family

Date of the actual completion of the international search

June 14, 1993 (14. 06. 93)

Date of mailing of the international search report

July 6, 1993 (06. 07. 93)

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(11) **EP 0 591 554 B1**

(12)

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13.11.1996 Bulletin 1996/46

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PCT/JP93/00535

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WO 93/22690 (11.11.1993 Gazette 1993/27)

(54) ACCELERATION SENSOR AND ITS MANUFACTURE

BESCHLEUNIGUNGSSENSOR UND SEINE HERSTELLUNG

CAPTEUR D'ACCELERATION ET SON PROCEDE DE FABRICATION

(84) Designated Contracting States:
DE GB

(30) Priority: 27.04.1992 JP 108020/92

(43) Date of publication of application:
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(56) References cited:
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JP-A-62 027 666 **JP-A-62 207 917**
US-A- 4 679 434

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EP 0 591 554 B1

Description

TECHNICAL FIELD

The present invention relates to an acceleration sensor, and more specifically, a semiconductor type acceleration sensor suitable for air-bag system, suspension control system, or the like, for automobiles.

BACKGROUND TECHNIQUES

In producing a semiconductor type acceleration sensor, the movable part thereof has hitherto been prepared in such a way that it penetrates a singlecrystal silicon wafer. Accordingly, a size large enough to penetrate through the thickness of a wafer is required, and therefore, it has been difficult to miniaturize the acceleration sensor. In addition, in order to incorporate this sensor into a package, there has been required a relaxation part such as a pedestal in order to release the stress caused by the difference in coefficients of thermal expansion or the like.

However, in Nikkei Electronics, November 11, 1991 (No. 540), pp 223 to 231, there is illustrated an acceleration sensor produced by use of a surface micro-machining technique. That is, a thin polysilicon film is laminated on a silicon substrate, and thereafter, this polysilicon film is etched, whereby a beam movable parallel to the surface of the substrate is formed, so as to form a differential capacity type acceleration sensor. However, when a beam structure is formed by use of polysilicon, if a signal processing circuit is formed around the formed beam structure, the sensor characteristics become unstable. This is because the beam structure is formed of a polycrystalline and amorphous material, resulting in noticeable variation for every production lot.

U.S. Patent No. 4,679,434 discloses an accelerometer in which a silicon substrate with an inertial mass movable by an acceleration is sandwiched by insulative layers 26 and 28. A change of the capacitor caused by approaching the inertial mass toward the insulative layers due to acceleration is detected to determine the acceleration.

Accordingly, it is still desirable to form an acceleration sensor by surface micro-machining singlecrystal silicon.

Under such circumstances, the purpose of the present invention is to provide an acceleration sensor having a novel structure, by which high precision and high reliability can be realized.

In addition, another purpose of the present invention is to produce this acceleration sensor with a good yield rate during the production process thereof.

DISCLOSURE OF THE INVENTION

This purpose is achieved by an acceleration sensor as defined in claim 1 and by processes for producing

same as defined in claim 4 to 11.

The gist of a first aspect of the invention resides in an acceleration sensor, comprising a second singlecrystal silicon substrate bonded onto a first singlecrystal silicon substrate with an insulating film interposed therebetween the second singlecrystal silicon substrate being made of a thin film, a beam formed on at least either of said first and second singlecrystal silicon substrates and movable in a direction parallel to the surface thereof, and a signal-processing circuit formed on at least one of said first and second singlecrystal silicon substrates for performing processing of signals produced by a movement of said beam, caused by an acceleration.

In addition, the gist of a second aspect of the invention resides in a process for producing an acceleration sensor, comprising; a first step of forming, on a main surface of a first singlecrystal silicon substrate, a groove with a predetermined depth for formation of a beam; a second step of forming, on the main surface of said first singlecrystal silicon substrate, a film of a polycrystalline silicon, an amorphous silicon or a mixture thereof so as to fill said groove with said silicon film, and smoothing (flattening) the surface of said silicon film; a third step of bonding the main surface of said first singlecrystal silicon substrate to a second singlecrystal silicon substrate with an insulating film formed thereon, said insulating film being interposed between said first and second singlecrystal silicon substrates; a fourth step of polishing the reverse side of said first singlecrystal silicon substrate to a predetermined degree, so as to make said first singlecrystal silicon substrate a thin film; and a fifth step of forming a signal-processing circuit on at least either of said first and second singlecrystal silicon substrates, and thereafter, removing by etching said silicon film of a polycrystal silicon, an amorphous silicon or a mixture thereof from said reverse side of said first singlecrystal silicon substrates, to form a beam.

In addition, the gist of a third aspect of the invention resides in a process for producing an acceleration sensor, comprising; a first step of bonding a main surface of a first singlecrystal silicon substrate to a second singlecrystal silicon substrate with an insulating film formed thereon, said insulating film being interposed therebetween; a second step of polishing the reverse side of said first singlecrystal silicon substrate to a predetermined degree, so as to make the first singlecrystal silicon substrate a thin film; a third step of forming a groove with a predetermined depth for formation of a beam; a fourth step of forming, on the reverse side of said first singlecrystal silicon substrate, a film of a polycrystal silicon, an amorphous silicon or a mixture thereof, so as to fill said groove with said silicon film, and smoothing the surface of said silicon film; and a fifth step of forming a signal-processing circuit on at least one of said first and second singlecrystal silicon substrates, and thereafter, removing by etching said film of polycrystal silicon, amorphous silicon or a mixture thereof from the reverse side of the first singlecrystal silicon substrate, to form a

beam.

According to the first aspect, when an acceleration is applied in a direction parallel to the surface of the bonded singlecrystal silicon substrates, the beam formed on the first or second singlecrystal silicon substrate moves. As this beam moves, signal processing is performed in the signal-processing circuit formed on the first or second singlecrystal silicon substrate.

According to the second aspect, as a first step, a groove of a predetermined depth for formation of a beam is formed on the main surface of the first singlecrystal silicon substrate, and as a second step, a film of a polycrystalline silicon, an amorphous silicon or a mixture thereof is formed on the main surface of the first singlecrystal silicon substrate, whereby the groove is filled with the silicon film, and the surface of this silicon film is flattened. Subsequently, as a third step, the main surface of the first singlecrystal silicon substrate is bonded to a second singlecrystal silicon substrate having an insulating film formed thereon, said insulating film being interposed between the first and second singlecrystal substrates, and, as a fourth step, the reverse side of the first singlecrystal silicon substrate is polished to a predetermined degree, whereby the first singlecrystal silicon substrate is made into a thin film. Subsequently, as a fifth step, a signal-processing circuit is formed on the first or second singlecrystal silicon substrate, whereafter the polycrystalline, amorphous or mixed silicon film is removed by etching from the reverse side of the first singlecrystal silicon substrate, and a beam is formed. As a result, an acceleration sensor according to the first aspect of the invention is produced.

According to the third aspect, as a first step, the main surface of a first singlecrystal silicon substrate is bonded to a second singlecrystal silicon substrate with an insulating film formed thereon, said insulating film being interposed between the first and second substrates, and as a second step, the reverse side of the first singlecrystal silicon substrate is polished to a predetermined degree, so that the first singlecrystal silicon substrate is made into a thin film. Subsequently, as a third step, a groove of a predetermined depth for formation of a beam is formed on the reverse side of the first singlecrystal silicon substrate, and as a fourth step, a film of polycrystalline silicon, an amorphous silicon or a mixture thereof is formed on the reverse side of the first singlecrystal silicon substrate, whereupon the groove is filled with the silicon film, and the surface of the silicon film is flattened. Subsequently, as a fifth step, a signal-processing circuit is formed on the first or second singlecrystal silicon substrate, whereafter the polycrystalline, amorphous or mixed silicon film is removed by etching from the reverse side of the first singlecrystal silicon substrate, and a beam is formed. As a result, an acceleration sensor according to the first aspect of the invention is produced.

BRIEF DESCRIPTION OF THE DRAWINGS

Fig. 1 is a plan of an acceleration sensor according to the first embodiment of the present invention, and Fig. 2 is a figure illustrating a section taken along the line A-A in Fig. 1.

Figs. 3 to 10 are illustrations for explanation of the manufacturing process of the first embodiment, and, respectively, sectional view for each production stage.

Fig. 11 is a plan illustrating an application example of the first embodiment, and Fig. 12 is a sectional view taken along the line B-B in Fig. 11.

Figs. 13 to 21 are illustrations for explanation of the manufacturing process of the second embodiment, and, respectively, a sectional view for each production stage.

Figs. 22 to 28 are illustrations for explanation of the manufacturing process of the third embodiment, and, respectively, a sectional view for each production stage.

Figs. 29 to 31 are illustrations for explanation of the manufacturing process of the fourth embodiment, and, respectively, a sectional view for each production stage.

Figs. 32 to 34 are illustrations for explanation of the manufacturing process examples to which the fourth embodiment is applied, and, respectively, a sectional view for each production stage.

Fig. 35 is a plan illustrating an example of a sensor tip formed by use of an acceleration sensor according to the present invention.

MOST PREFERRED EMBODIMENTS FOR WORKING THE INVENTION

In the following, the embodiments of the present invention, will be explained with reference to the attached drawings.

First Embodiment

Fig. 1 is a view plan of an acceleration sensor produced by the first embodiment of the production process of the present invention, and Fig. 2 is a sectional view taken along the line A-A in Fig. 1. In addition, in the present embodiment, the sensor part and the signal-processing circuit are formed of the same singlecrystal silicon substrate.

The present acceleration sensor is a capacity type acceleration sensor. As illustrated in Fig. 2, there is bonded onto a singlecrystal silicon substrate 8 a singlecrystal silicon substrate 1 through an SiO₂ film 9, and in the singlecrystal silicon substrate 1, there is formed a cantilever 13 by a trench 3 penetrating said substrate 1. As illustrated in Fig. 1, this cantilever 13 has a structure such that an end side thereof is branched into two parts. The cantilever 13 can be moved in a direction parallel to the surface of the singlecrystal silicon substrate 1 (the arrow direction C in Fig. 1). In addition, in the singlecrystal silicon substrate 1, a signal-processing circuit 10 is formed and is electrically insulated from the cantilever

13 by a polysilicon film 6 and an SiO₂ film 5.

In the following, the first embodiment of the production process of the present invention, which is suitable for the production of the aforesaid structure, will be explained with reference to Figs. 3 to 10.

First, as illustrated in Fig. 3, an n-type (100) single-crystal silicon substrate 1 with a resistance of 1 to 20Ω·cm is provided, and on the main surface thereof, there is formed an SiO₂ film 2 with a thickness of about 1 μm by thermal oxidation, and the SiO₂ film 2 is formed into a predetermined pattern by a photolithographic method. This pattern is a pattern exposing, on the main surface of the silicon substrate, an area to be formed as a groove separating at least an area to be formed as a movable electrode (cantilever) from the substrate, and in the present embodiment, this pattern is formed as a pattern exposing also the main surface of the silicon substrate in an area for transversely insulating and separating the signal-processing circuit. Subsequently, on the main surface side of the singlecrystal silicon substrate 1, there is formed a trench 3 having a perpendicular wall with a predetermined depth, e.g. ranging from about 0.2 to about 30 μm. In the present embodiment, explanation will be made with respect to the case where the wall thickness is about 3 μm.

Subsequently, after the SiO₂ film 2 has been removed, as illustrated in Fig. 4, an n⁺ diffused layer 4 formed using phosphorus, arsenic or the like is formed on the main surface of the singlecrystal silicon substrate 1, including the internal wall of the trench 3, and further, an SiO₂ film 5 with a thickness ranging from 0.1 to 1 μm is formed by thermal oxidation or the like. In this case, in order to prevent damage by etching, there may be conducted the so-called "sacrifice oxidation" in which SiO₂ is formed by thermal oxidation and removed before formation of the n⁺ diffused layer 4.

Subsequently, as illustrated in Fig. 5, a polysilicon film 6 is formed on the main surface of the singlecrystal silicon substrate 1, and the trench 3 is filled with the polysilicon film 6. In addition, in the case where an impurity is introduced into the polysilicon film 6 in order to use the polysilicon film 6 as a conductive path, forming a thin polysilicon layer and diffusing phosphorus or the like in a high concentration before formation of the polysilicon film 6, allows the impurity to be introduced into the polysilicon film 6.

Next, as illustrated in Fig. 6, the surface of the polysilicon film 6 is mirror finished, so as to make the thickness of the polysilicon film 6 a predetermined value. Subsequently, boron ions or other impurity are implanted into the polysilicon film 6 to form p⁺ diffused layers 7 in predetermined areas.

On the other hand, as illustrated in Fig. 7, another (100) singlecrystal silicon substrate 8 is provided, and an SiO₂ film 9 with a thickness ranging from 0.1 to 1.0 μm is formed on the main surface of the silicon substrate 8.

Subsequently, the singlecrystal silicon substrate 1

and the singlecrystal silicon substrate 8 are dipped into e.g. an aqueous mixed solution of aqueous hydrogen peroxide and sulfuric acid, so as to subject these substrates to a hydrophilicity-imparting treatment. Thereafter, these substrates are dried, and as illustrated in Fig. 8, the main surface of the singlecrystal silicon substrate 1 and that of the singlecrystal silicon substrate 8 are put together at room temperature, and these substrates are introduced into a furnace at 400 to 1100°C for a period of time ranging from 0.5 to 2 hours, so as to strongly bond them.

Subsequently, as illustrated in Fig. 9, by use of an aqueous solution of an alkali type, e.g. an aqueous KOH solution or the like, the reverse side of the singlecrystal silicon substrate 1 is subjected to selective polishing. The polishing is continued until the SiO₂ film 5 is exposed. As a result, the thickness of the singlecrystal silicon substrate 1 reaches a value which is approximately determined by the depth of the trench, e.g. about 3 μm, so that the substrate 1 is made thin.

Subsequently, as illustrated in Fig. 10, in a predetermined area of the singlecrystal silicon substrate 1, there is formed a signal-processing circuit 10 (IC circuit portion) by use of an ordinary CMOS process, bipolar process or the like. In addition, a diffused layer for connecting to wiring and a metallic electrode film composed of an aluminum film or the like are formed, and wiring at the sensor part, wiring at the circuit part, and connection of the sensor part to the circuit part are performed. In Fig. 1 and Fig. 10, a MOS transistor alone is illustrated as a part of the signal-processing circuit 10.

Further, on the upper surface of the signal-processing circuit 10, there is formed, as a passivation film 11, a plasma SiN film (P-SiN) e.g. by a plasma CD method. Subsequently, at the sensor part side, windows 12 are opened at predetermined areas of the passivation film 11, and the polysilicon film 6 filled in the trench 3 is exposed from the surface. By this window opening procedure, the singlecrystal portions where a cantilever or fixed electrodes are to be formed are demarcated from the polycrystal portions embedded in the trench, on the surface of the substrate.

Subsequently, as illustrated in Fig. 2, by use of a 20% solution of TMAH (tetramethylammonium hydroxide) (CH₃)₄NOH, the polysilicon film 6 is removed by etching through the windows 12 of the passivation film 11, from the reverse side (the upper side in Fig. 2) of the singlecrystalline silicon substrate 1. In this case, the passivation film 11 (P-SiN), SiO₂ film 5, aluminum wiring layer and p⁺ diffused layer (p⁺ polysilicon film) 7 are hardly etched by the selective etching. Accordingly, the bonding of the singlecrystal silicon substrate to the lower singlecrystal silicon substrate 8 is secured through the p⁺ diffused layer (p⁺ polysilicon film) 7.

In addition, if trenches 3 are preliminarily formed also in the wide area of the cantilever 13 in Fig. 1, and etching windows 48 are provided simultaneously with the formation of the windows 12, in such a way that the

etching windows 48 communicate with said trenches 3, the polysilicon film 6 below the movable part (cantilever 13) of the sensor can be more securely removed by etching through this etching window 48 when the polysilicon film 6 is removed by etching.

By the aforesaid procedures, the cantilever 13 is formed. In this case, the cantilever 13 becomes, as illustrated in Fig. 2, smaller in the thickness L2 in a direction parallel to the surface of the singlecrystal silicon substrate 1 than in the thickness L1 in a direction along the depth of the singlecrystal silicon substrate 1.

In a capacity type acceleration sensor, the end portions (bifurcated portions) of the cantilever 13 are formed as movable electrodes, and as illustrated in Fig. 1, the parts of the singlecrystal silicon substrate 1, opposing the end portions of the cantilever 13, are formed as fixed electrodes 14, 15, 16, and 17, respectively. In addition, as illustrated in Fig. 1, fixed electrode 14 and fixed electrode 16 are derived through an aluminium wiring layer 18a, fixed electrode 15 and fixed electrode 17 are derived through an aluminium wiring layer 18b, and the cantilever 13 (movable electrode) is derived through an aluminium wiring layer 18c. These aluminium wiring layers 18a, 18b, and 18c are connected to the signal-processing circuit 10, and by this signal-processing circuit 10, signal processing is conducted as the cantilever (movable electrode) 13 is displaced owing to an acceleration. In addition, by the n⁺ diffused layers 4 (see Fig. 2) disposed on the cantilevers 13 (movable electrodes) and fixed electrodes 14, 15, 16, and 17, the electric potential is maintained at a constant value.

Although a capacity type acceleration sensor is made in the present embodiment, if a piezo resistance layer is formed at the surface of the root portion of the cantilever 13, a piezo resistance type acceleration sensor can be formed. If these two types of sensors are formed in a one and same substrate, the precision and reliability of the acceleration sensor can further be improved.

In the acceleration sensor thus produced, the singlecrystal silicon substrate 1 is bonded through an SiO₂ film to the singlecrystal silicon substrate 8, so as to form an SOI structure. In addition, in the cantilever 13, its thickness L2 in a direction parallel to the surface of the singlecrystal silicon substrate 1 is smaller than the thickness L1 in a direction of the depth of the singlecrystal silicon substrate 1. Accordingly, the cantilever 13 becomes movable, on the surface of the singlecrystal silicon substrate 1, in a direction parallel to the surface, whereby an acceleration to a direction parallel to the substrate surface is detected.

As mentioned in the foregoing, in the present embodiment, on the main surface of the singlecrystal silicon surface 1, there is formed a trench (groove) 3 of a predetermined depth for formation of the cantilever 13 (the first step), and the polysilicon film 6 is formed on the main surface of the singlecrystal silicon substrate 1, so as to fill the trench 3 with said polysilicon film 6, and

the surface of the polysilicon film 6 is flattened (smoothed) (the second step). Subsequently, the main surface of the singlecrystal silicon substrate 1 is bonded to the singlecrystal silicon substrate 8 with an SiO₂ film 9 (insulating film) formed thereon, through said SiO₂ film 9 being interposed between the substrates 1 and 8 (the third step), whereafter the reverse side of the singlecrystal silicon substrate 1 is polished to a predetermined degree, so as to make the singlecrystal silicon substrate into a thin film (the fourth step). Subsequently, the signal-processing circuit 10 is formed on the surface of the singlecrystal silicon substrate, whereafter the polysilicon film 6 is removed by etching from the reverse side of the singlecrystal silicon substrate, so as to form the cantilever 13 (the fifth step).

Accordingly, during the process for the formation of the signal-processing circuit 10, in the course of the wafer process, the trench 3 in the surface portion of the singlecrystal silicon substrate, is filled with the polysilicon film 6, whereby contamination of the IC elements, contamination of production equipment, and degradation or deterioration of electrical properties accompanied therewith can be prevented. That is, in the wafer process, by contriving to prevent the surface structures such as concave portions or penetration holes from appearing on the wafer surface in the heat treatment, photolithographic treatment and the like, in the course of the process, it is possible to prevent contamination and the like, and to thereby stably provide acceleration sensors of high precision.

The thus produced acceleration sensor comprises the singlecrystal silicon substrate 1, which is bonded through an SiO₂ film (insulating film) to the singlecrystal silicon substrate 8, and which is made a thin film; the cantilever 13, which is formed on said singlecrystal silicon substrate 1 and which is movable in a direction parallel to the surface of the substrate; and the signal-processing circuit 10, which is also formed on the singlecrystal silicon substrate 1 and which performs signal processing as the cantilever 13 moves owing to an acceleration. When an acceleration is applied in a direction parallel to the surface of the singlecrystal silicon substrate 1, the cantilever formed on the singlecrystal silicon substrate 1 moves. As the cantilever 13 moves, signal-processing is performed by the signal-processing circuit 10 formed on the singlecrystal silicon substrate 1. In such a way as above, by a micro-machining technique using singlecrystal silicon, an acceleration sensor is formed, by the novel structure of which high precision and high reliability can be realized.

In addition, since the surface of the aforesaid cantilever 13 and the part of the singlecrystal silicon substrate 1, opposing said cantilever 13, are coated with the SiO₂ film (insulator) 5, electrode short-circuit in the capacity type acceleration sensor can previously be prevented. In addition, it suffices if at least either of the surface of the cantilever 13 or the part of the singlecrystal silicon substrate 1 opposing the cantilever 13 is coated

with the SiO₂ film (insulator) 5.

Further, as an application of the present embodiment, as illustrated in Figs. 11 and 12, the cantilever may be separated from the signal-processing circuit (IC circuit portion) 10 and an air bridge wiring is formed, in order to reduce parasitic capacity. In addition, the fixed electrodes 14, 15, 16, and 17 may be formed so as to have the same structure as above. This can be realized by forming a p⁺ type polysilicon film 7 at the minimum position necessary for bonding the fixed electrodes to the lower substrate.

In addition, although an aluminium wiring layer is used in the aforesaid embodiment, the wiring part may be formed by use of a polysilicon layer. Further, although two movable electrodes are formed at the end of the beam and simultaneously, four fixed electrodes 14, 15, 16, and 17 are formed, in the aforesaid embodiment, the movable and fixed electrodes may be formed like the teeth of a comb in order to further improve the sensitivity of the sensor.

In addition, an oxide film may selectively be formed, instead of the formation of the p⁺ polysilicon film 7.

Second Embodiment

Next, there will be made explanations about the production process in the second embodiment, laying stress on the points different from those in the first embodiment. In addition, in the second embodiment to be hereafter explained, explanations will be made by way of example of the case where a sensor having a structure according to the structure illustrated in Figs. 1 and 2 as explained in the aforesaid first embodiment, and there will be illustrated a sectional view corresponding to the A-A section of Fig. 1.

In the aforesaid first embodiment, in order to form the cantilever 13, the p⁺ diffused layer (p⁺ polysilicon film) 7 is formed for the purpose of separating the cantilever portion from the singlecrystal silicon substrate at a predetermined distance, but in the present embodiment, a concave portion is formed before formation of a trench, for the purpose of separating the cantilever from the substrate at a predetermined distance.

In Figs. 13 to 21, the production process is illustrated.

First, as illustrated in Fig. 13, an n type (100) singlecrystal silicon substrate 20 is provided, and on the main surface of the provided singlecrystal silicon substrate 20, there is formed a concave portion 21 with a predetermined depth e.g. ranging from 0.1 to 5 μm. Subsequently, as illustrated in Fig. 14, on the main surface of the singlecrystal silicon substrate 20, there is formed an SiO₂ film 22, and a pattern is formed by a photolithographic means, in the same way as in the aforesaid first embodiment. Subsequently, on the main surface of the singlecrystal silicon substrate 20 including the bottom of the concave portion 21, there is formed a trench with a depth ranging from about 0.1 to about 30 μm (3

μm in the present embodiment) by dry etching or the like.

Subsequently, as illustrated in Fig. 15, on the main surface of the singlecrystal silicon substrate 20 including the internal wall of the trench 23, there is formed an n⁺ diffused layer 24, and an SiO₂ film 25 is formed by thermal oxidation. Thereafter, as illustrated in Fig. 16, a polysilicon film 26 is deposited in the trench 23 by the LPCVD method.

Subsequently, as illustrated in Fig. 17, the surface of the polysilicon film 26 is polished by use of the SiO₂ film as an etching stopper, so as to smooth the surface. In the above case, although it is desirable that the surfaces of the polysilicon film 26 and the SiO₂ film 25 become smooth, even if the polysilicon film 26 is rather indented, so long as the surface of the SiO₂ film is made smooth, no inconvenience is caused in the subsequent wafer cementing.

On the other hand, as illustrated in Fig. 18, another (100) singlecrystal silicon substrate 27 is provided, and, on the main surface of the substrate 27, there is formed an SiO₂ film with a thickness ranging from 0.1 to 1.0 μm by thermal oxidation of the substrate. Subsequently, singlecrystal silicon substrates 20 and 27 are dipped in e.g. a solution of an aqueous hydrogen peroxide and sulfuric acid, so as to subject them to a hydrophilicity-imparting treatment. Subsequently, the substrates are dried, and thereafter, the main surfaces of the two singlecrystal silicon substrates 20 and 27 are put together at room temperature, and introduced into a furnace at 400 to 1100°C for a period of time ranging from 0.5 and 2 hours, so as to strongly bond the two surfaces.

Subsequently, as illustrated in Fig. 19, the reverse side of the singlecrystal silicon substrate 20 is subjected to selective polishing by use of an aqueous solution of alkali type, e.g. an aqueous KOH solution. The selective polishing is performed until the SiO₂ film 25 appears on the surface. As a result, the thickness of the singlecrystal silicon substrate 20 becomes e.g. about 3 μm, so as to be made a thin film.

Subsequently, as illustrated in Fig. 20, a signal-processing circuit (IC circuit portion) 10 is formed through an ordinary CMOS process, bipolar process, or the like. Further, on the upper surface of the signal-processing circuit 10, there is formed, as a passivation film 11, a plasma SiN film (P-SiN film) by e.g. plasma CVD method. Subsequently, windows 12 are opened at predetermined areas of the passivation film 11, and the polysilicon film 20 is exposed to the surface at the sensor portion.

Subsequently, as illustrated in Fig. 21, by use of a 20% solution of TMAH (tetramethylammonium hydroxide) (CH₃)₄NOH, the polysilicon film 26 is removed by etching from the reverse side of the singlecrystal silicon substrate 20 through the windows 12 on the passivation film 11. In the above case, the passivation film 11 (P-SiN), SiO₂ film, and aluminium wiring layer are hardly etched by the selective etching.

As a result, a cantilever 13 is formed.

Also by the present embodiment, there is obtained the same effect as in the aforesaid first embodiment.

Third Embodiment

Next, there will be made explanations about the production process in the third embodiment, laying stress on the differential points between the first and third embodiments.

Although, in the aforesaid first and second embodiments, the trench is filled with polysilicon before the bonding of the wafers, in the present embodiment, the trench is filled with polysilicon after the bonding of wafers, and in the final stage, the thus filled polysilicon is removed, so as to produce an acceleration sensor.

In Figs. 22 to 28, the production process is illustrated.

First, as illustrated in Fig. 22, an n-type (100) singlecrystal silicon substrate 30 is provided, and on the main surface of the provided singlecrystal silicon substrate 30, there is formed a concave portion 31 in a depth ranging from 0.1 to 5 μm , in the same way as in the aforesaid second embodiment. On the other hand, as illustrated in Fig. 23, a singlecrystal silicon substrate 32 is provided, and an SiO_2 film is formed by thermal oxidation on the main surface of the singlecrystal silicon substrate 32. Thereafter, the main surface of the singlecrystal silicon substrate 30 is bonded to the main surface of the single crystal silicon substrate 32.

Subsequently, as illustrated in Fig. 24, the reverse side of the singlecrystal silicon substrate 30 is subjected to mirror polishing to a predetermined thickness (0.1 to 30 μm). Thereafter, as illustrated in Fig. 25, there is formed an SiO_2 film 34 to a thickness ranging from 0.1 to 2 μm , following which the SiO_2 film is subjected to patterning, and a trench 35 is formed by etching. Thereby, a cantilever 13 and a transversal insulatedly separated area of the processing circuit portion are formed.

Next, by thermal diffusion or the like, there is introduced an N type impurity of arsenic or phosphorus in a high concentration, and a highly concentrated n^+ layer 36 is formed in the silicon area which is not covered with SiO_2 films 33 and 34.

Subsequently, as illustrated in Fig. 26, a thermal oxidation film is formed on the side wall of the trench 35 and the like, whereafter a polysilicon film 37 is formed on the surface of the singlecrystal silicon substrate 30, and the trench 35 is filled with the polysilicon film 37. Thereafter, as illustrated in Fig. 27, the surface of the polysilicon film 37 is selectively polished and smoothed until the SiO_2 film 34 appears on the surface. Further, as illustrated in Fig. 28, a signal-processing circuit 10 is formed, and finally, the polysilicon film 37 is removed by etching from the reverse side (upper surface side) of the singlecrystal silicon substrate 30, so as to again separate the cantilever 13 from the substrate to allow it to move.

As described above, in the present third embodiment, the main surface of the singlecrystal silicon substrate 30 is bonded to the singlecrystal silicon substrate 32 with the SiO_2 film (insulating film) 33 formed thereon, through said SiO_2 film 33 being interposed between the substrates 30 and 32 (first step), and the reverse side of the singlecrystal silicon substrate is polished to a predetermined degree, so as to make the singlecrystal silicon substrate 30 a thin film (second step). Subsequently, on the reverse side of the singlecrystal silicon substrate 30, there is formed a trench (groove) 35 with a predetermined depth for formation of a cantilever 13 (third step), and the trench 35 is filled with the polysilicon film 37, and the surface of the polysilicon film 37 is smoothed (fourth step). Subsequently, a signal-processing circuit is formed on the singlecrystal silicon substrate 30, whereafter the polysilicon film 37 is removed, by etching, from the reverse side of the singlecrystal silicon substrate 30, so as to form a cantilever 13 (fifth step).

Therefore, in the process of formation of the signal-processing circuit 10 in the wafer, the trench 35 is filled with the polysilicon film 37 in the upper surface part of the singlecrystal silicon substrate 30, whereby contamination of the IC elements, contamination of the production apparatus, and degradation or deterioration of electrical properties attended therewith can be prevented. That is, by contriving not to make a surface structure such as a concave portion or a perforation of the like appear on the wafer surface in the heat treatment, the photolithographical treatment or the like in the course of the wafer process, contamination and the like can be prevented, so as to stabilize the wafer process, and a stable supply of acceleration sensors, of high precision, can be produced.

Fourth Embodiment

In the following, there will be made explanations about the production process of the fourth embodiment, laying stress on the differences between the present embodiment and the third embodiment.

The present embodiment is intended to produce an acceleration sensor at a lower cost than the production process of the third embodiment.

In Figs. 29 to 31, the production process is illustrated.

First, as illustrated in Fig. 29, an SiO_2 film with a thickness ranging from 0.1 to 2 μm is formed on the main surface of a singlecrystal silicon substrate 40, and a singlecrystal silicon substrate 42 is bonded to the substrate 40 so as to interpose the SiO_2 film 41 between the substrates 40 and 42. Subsequently, as illustrated in Fig. 30, the upper surface of the singlecrystal silicon substrate 42 is polished so as to make the thickness of the singlecrystal silicon substrate a predetermined value. That is, the thickness of the singlecrystal silicon substrate 42 is reduced to e.g. about 3 μm . Thereafter, a

highly concentrated n⁺ diffused layer 43 is formed on the upper surface of the singlecrystal silicon substrate 42, and further, an SiO₂ film 44 is formed thereon. It suffices if this highly concentrated n⁺ diffused layer 43 is formed corresponding to the parts of the sensor which will be formed as movable electrodes and fixed electrodes.

Subsequently, as illustrated in Fig. 31, patterning is applied to an SiO₂ film, as in the third embodiment, and a trench 45 is formed on the singlecrystal silicon substrate 42. Thereafter, the SiO₂ film 41 below this trench 45 is partly removed by etching with an aqueous hydrofluoric acid solution. In this case, a part of SiO₂ film 41, below the part to be formed as a cantilever 13, is completely removed, and another part of the SiO₂ film 41, below the part to be formed as solid electrodes and signal-processing circuit portion, is left. Because the lower portion of the part is to be formed as the cantilever 13 it is narrower than with the other part. In addition, in the above case, the highly concentrated n⁺ diffused layer 43 is separated into the cantilever 13 and fixed electrodes.

Subsequently, through the same processes as illustrated in Figs. 26 to 28, there is produced a capacity type acceleration sensor.

In the following, there will be explained application examples of the fourth embodiment with reference to Figs. 32 to 34.

First, as illustrated in Fig. 32, an SiO₂ film with a thickness ranging from 0.1 to 2 μm is formed on the main surface of the singlecrystal silicon substrate 40, and a concave portion 47 with a depth ranging from 0.1 to 3 μm is formed at the area of the main surface of the singlecrystal silicon substrate 42, on which area a cantilever is to be formed. Subsequently, the main surface of the singlecrystal silicon substrate 42 is bonded to the main surface of the singlecrystal silicon substrate 40, the SiO₂ film 41 being put therebetween. Further, as illustrated in Fig. 33, the upper surface of the singlecrystal silicon substrate 42 is polished so as to give the singlecrystal silicon substrate 42 a predetermined thickness. That is, the thickness of the singlecrystal silicon substrate 42 is made thin to a value of about 3 μm. Subsequently, the aforesaid highly concentrated diffused layer 43 is formed on the upper surface of the singlecrystal silicon substrate 42, and an SiO₂ film 44 is formed thereon.

Subsequently, as illustrated in Fig. 34, onto the singlecrystal silicon substrate 42, there are formed trenches 45 extending to the concave portions 47, and cantilevers 13 are formed.

Thereafter, a capacity type acceleration sensor is produced through the same processes as illustrated in Figs. 26 to 28.

By conducting the aforesaid procedures, electrical insulation can be made more securely as compared with the case where the SiO₂ film 41 is partly removed by etching. In addition, the mechanical strength of the sen-

sor can be improved.

In addition, the present invention is not restricted to the aforesaid embodiments, and is applicable to a twin-lever spring or a polylever spring embodiment, in addition to a cantilever spring embodiment.

In addition, as illustrated in Fig. 35, it is possible to form two acceleration sensors 13a and 13b onto a singlecrystal silicon substrate 50, for detecting the acceleration in the direction X by the acceleration sensor 13a, and the acceleration in the direction Y by the acceleration sensor 13b. Further, it is possible to form an acceleration sensor capable of detecting the acceleration in a direction surface perpendicular to these X and Y direction acceleration sensors 13a and 13b, on the same substrate, so as to detect an acceleration in three-dimensions. In addition, when the present acceleration sensor is used as a capacity type acceleration sensor, it is possible to further stabilize the properties by forming the present acceleration sensor into a so-called "servo type" sensor (with a closed-loop circuit).

In addition, in the aforesaid embodiments, the trenches (grooves) 3, 23, and 35 are filled with polysilicon films 6, 26, and 37, respectively, but there may be used a film of polysilicon, amorphous silicon or a mixed silicon containing polysilicon and amorphous silicon.

In addition, in the aforesaid embodiments, a sensor portion and a signal-processing portion are formed in the singlecrystal silicon substrate to be formed as the upper side, but the present acceleration sensor is not restricted to such a structure, and it is possible to utilize also a singlecrystal silicon substrate formed as a base, and form a sensor portion and a signal-processing portion on the lower substrate.

As described in detail in the foregoing, according to the present invention, high precision and high reliability can be realized by formatting a novel structure. In addition, when a signal-processing circuit is provided on the same chip as a movable beam, since there is produced neither a hollow part nor a groove during the production process, it is possible to make the processing stable. In addition, it is at the final step that the movable beam is made movable with respect to the substrate, whereby, in the case of the movable beam being bonded to the lower substrate to be formed as a pedestal or in the case of a circuit being formed, or the like, minute beams can be prevented from being broken, and the yield thereof can be made higher. In addition, since it is a micro-machining technique which determines the shape of the present acceleration sensor, the present acceleration sensor can be produced with high precision.

[Industrial Availability]

As described in the foregoing, the present invention is useful for the production of a semi-conductor acceleration sensor having minute movable parts, and the present acceleration sensor is suitable as an acceleration sensor to be used for air bag system, suspension

control system and the like of automobiles. In addition, the present invention can be applied to a capacity type acceleration sensor for detecting acceleration in multiple directions.

Claims

1. An acceleration sensor, characterized in that it comprises:

a second singlecrystal silicon substrate (8; 27; 32; 40), which is bonded onto a first singlecrystal silicon substrate (1; 20; 30; 42), an insulating film (9; 28; 33; 41) being interposed between the substrates;
a movable beam (13), formed on at least one of said first or second singlecrystal silicon substrates, and which is movable in a direction (C) parallel to the surface of the substrate; and
a signal-processing circuit (10), formed on at least one of the said first or second singlecrystal silicon substrates for performing processing of signals produced by a movement of said beam caused by acceleration.

2. An acceleration sensor as claimed in claim 1, wherein said beam (13) is smaller in thickness in a direction parallel to the surface of said singlecrystal silicon substrates (1, 8; 20, 27; 30, 32; 40, 42) as compared to the thickness in a direction of the depth of said singlecrystal silicon substrates.

3. An acceleration sensor as claimed in claim 1, wherein at least one of the surface of said beam (13) and the surface of the second singlecrystal silicon substrate (8; 27; 32; 40) opposing said beam is covered with an insulator (5, 9; 25, 28; 33, 34).

4. A process for producing an acceleration sensor, comprising:

a first step of forming, on a main surface of a first singlecrystal silicon substrate (1; 20), a groove of a predetermined depth at an area surrounding a movable beam (13) to be formed;
a second step of depositing, on the main surface of said first singlecrystal silicon substrate (1; 20), a film (6; 26) of a polycrystalline silicon, amorphous silicon or a mixture thereof, so as to fill said groove with said silicon film, and smoothing the surface of said silicon film;
a third step of bonding the main surface of said first singlecrystal silicon substrate (1; 20) to a second singlecrystal silicon substrate (8; 27) with an insulating film (9; 28) interposed therebetween;
a fourth step of polishing the surface of said first

singlecrystal silicon substrate (1; 20) on the reverse side, which is the side opposite to the main surface thereof, to a predetermined degree, so as to make the first singlecrystal silicon substrate a thin film; and

a fifth step of forming a signal processing circuit (10) on at least either of said first and second singlecrystal silicon substrates (1, 8; 20, 27), and thereafter, removing by etching said silicon film (6; 26) of polycrystalline silicon, amorphous silicon or a mixture thereof from said reverse side of said first singlecrystal silicon substrate (1; 20), to form said beam (13).

5. A process for producing an acceleration sensor as claimed in claim 4, wherein, in said first step, said predetermined depth is set according to the thickness of said beam (13) in the vertical direction thereof.

6. A process for producing an acceleration sensor as claimed in claim 4, wherein, in said third step, said insulating film (9; 28) is formed on the surface of said second singlecrystal silicon substrate (8; 27).

7. A process for producing an acceleration sensor as claimed in claim 4, wherein, in said second step, there remains said flat silicon film (6) on the main surface of said first singlecrystal silicon substrate (1).

8. A process for producing an acceleration sensor as claimed in claim 7, wherein, prior the said third step, there is added a step of making said silicon film (6) remaining on the main surface of said singlecrystal silicon substrate (1) to be resistant to the etching in said fifth step, except for the silicon film (6) positioned at an area surrounding said movable beam (13).

9. A process for producing an acceleration sensor as claimed in claim 4, wherein said first step additionally includes a step of forming a concave portion (21) on the main surface of said first singlecrystal silicon substrate (20), at the position where said beam (13) is to be formed.

10. A process for producing an acceleration sensor as claimed in claim 4, wherein, prior to said fifth step, there is added a step of forming a semi-conductor element (10) on said first (1; 20) or second (8; 27) singlecrystal silicon substrate.

11. A process for producing an acceleration sensor, comprising:

a first step of bonding the main surface of a first singlecrystal silicon substrate (30; 42) to a sec-

ond singlecrystal silicon substrate (32; 40) with an insulating film (33; 41) interposed therebetween;

a second step of polishing the surface of said first singlecrystal silicon substrate (30; 42) on the reverse side, which is the side opposite to the main surface thereof, to a predetermined degree, so as to make the first singlecrystal silicon substrate a thin film;

a third step of forming a groove in the first singlecrystal substrate (30; 42), the groove extending from the reverse side of the substrate (30; 42) to said insulating film (33; 41) in an area surrounding a movable beam (13) to be formed;

a fourth step of depositing, from the reverse side of the said first singlecrystal silicon substrate (30; 42), a film (37) of polycrystalline silicon, amorphous silicon, or a mixture thereof, so as to fill said groove with said silicon film, and smoothing the surface of said silicon film; and

a fifth step of forming a signal processing circuit (10) on at least one of said first and second singlecrystal silicon substrates (30, 32; 40, 42), and thereafter removing by etching said film (37) of polycrystalline silicon, amorphous silicon, or a mixture thereof from the reverse side of the first singlecrystal silicon substrate (30; 42), to form said beam (13).

12. A process for producing an acceleration sensor as claimed in claim 11, wherein, in said first step, said insulating film (33; 41) is formed on the surface of said second singlecrystal silicon substrate (33, 40).

13. A process for producing an acceleration sensor as claimed in claim 11, wherein said fifth step includes a step of removing said insulating film (41) at a position corresponding to the position where said beam (13) is formed.

14. A process for producing an acceleration sensor as claimed in claim 11, wherein said first step includes a step of forming, prior to said bonding, a concave portion (47) in an area of the main surface of said first singlecrystal silicon substrate (42), corresponding to the position where said beam (13) is to be formed.

Patentansprüche

1. Beschleunigungssensor, gekennzeichnet durch:

ein zweites einkristallines Siliziumsubstrat (8; 27; 32; 40), das auf ein erstes einkristallines Siliziumsubstrat (1; 20; 30; 42) durch Bondieren aufgebracht ist, wobei zwischen den Substra-

ten ein isolierender Film (9; 28; 33; 41) eingeschoben ist;

einen beweglichen Ausleger (13), der auf wenigstens dem ersten oder zweiten einkristallinen Siliziumsubstrat ausgebildet und der in einer Richtung (C) parallel zur Oberfläche des Substrates beweglich ist; und

eine Signalverarbeitungs-Schaltung (10), die auf wenigstens dem ersten oder zweiten einkristallinen Siliziumsubstrat ausgebildet ist, zum Ausführen der Verarbeitung von Signalen, die durch eine durch Beschleunigung verursachte Bewegung des Auslegers erzeugt werden.

2. Beschleunigungssensor nach Anspruch 1, worin der Ausleger (13) in Richtung parallel zur Oberfläche des einkristallinen Siliziumsubstrats (1, 8; 20, 27; 30, 32; 40, 42) eine geringere Dicke als in Richtung der Tiefe des einkristallinen Siliziumsubstrats aufweist.

3. Beschleunigungssensor nach Anspruch 1, worin wenigstens die Oberfläche des Auslegers (13) oder die dem Ausleger gegenüberliegende Oberfläche des zweiten einkristallinen Siliziumsubstrats (8; 27; 32; 40) mit einem Isolator (5, 9; 25, 28; 33, 34) belegt ist.

4. Verfahren zum Herstellen eines Beschleunigungssensors, umfassend:

einen ersten Schritt zum Ausbilden eines Einschnittes mit einer vorbestimmten Tiefe an einer einen zu bildenden, beweglichen Ausleger (13) umgebenden Fläche auf einer Hauptoberfläche eines ersten einkristallinen Siliziumsubstrats (1; 20);

einen zweiten Schritt zum Abscheiden eines Films (6; 26) aus einem polykristallinen Silizium, amorphen Silizium oder einer Mischung daraus auf der Hauptoberfläche des ersten einkristallinen Substrats (1; 20), so, daß der Einschnitt mit dem Siliziumfilm ausgefüllt wird, und zum Glätten der Oberfläche des Siliziumfilms;

einen dritten Schritt zum Bondieren der Hauptoberfläche des ersten einkristallinen Siliziumsubstrats (1; 20) an ein zweites einkristallines Siliziumsubstrat (8; 27) mit einem dazwischen eingelegten isolierenden Film (9; 28);

einen vierten Schritt zum Polieren der Oberfläche des ersten einkristallinen Siliziumsubstrats (1; 20) auf der Rückseite, die die der Hauptoberfläche davon gegenüber liegende Seite ist,

bis zu einem vorbestimmten Grad, so, daß das erste einkristalline Siliziumsubstrat ein dünner Film wird; und

einen fünften Schritt zum Bilden einer Signalverarbeitungsschaltung 10 auf wenigstens beiden des ersten und des zweiten einkristallinen Siliziumsubstrats (1, 8; 20, 27), und danach zum Entfernen des Siliziumfilms (6; 26) aus polykristallinem Silizium, amorphem Silizium oder einer Mischung davon durch Ätzen von der Rückseite des ersten einkristallinen Siliziumsubstrats (1; 20) aus, um den Ausleger (13) zu bilden.

5. Verfahren zum Herstellen eines Beschleunigungssensors gemäß dem Anspruch 4, worin im ersten Schritt die vorbestimmte Tiefe gemäß der Dicke des Auslegers (13) in der vertikalen Richtung davon gewählt wird. 5
6. Verfahren zum Herstellen eines Beschleunigungssensors gemäß dem Anspruch 4, worin im dritten Schritt der isolierende Film (9; 28) auf der Oberfläche des zweiten einkristallinen Siliziumsubstrats (8; 27) ausgebildet wird. 10
7. Verfahren zum Herstellen eines Beschleunigungssensors gemäß dem Anspruch 4, worin im zweiten Schritt der flache Siliziumfilm (6) auf der Hauptoberfläche des ersten einkristallinen Siliziumsubstrats (1) zurückbleibt. 15
8. Verfahren zum Herstellen eines Beschleunigungssensors gemäß dem Anspruch 7, worin dem dritten Schritt vorausgehend ein Schritt hinzugefügt wird, bei dem der auf der Hauptoberfläche des einkristallinen Siliziumsubstrats (1) verbleibende Siliziumfilm (6) beständig gegen das Ätzen im fünften Schritt gemacht wird, mit Ausnahme des auf einer den beweglichen Ausleger (13) umgebenden Fläche befindlichen Siliziumfilms (6). 20
9. Verfahren zum Herstellen eines Beschleunigungssensors gemäß dem Anspruch 4, worin der erste Schritt zusätzlich einen Schritt zum Bilden eines konkaven Teils (21) auf der Hauptoberfläche des ersten einkristallinen Siliziumsubstrats (20) einschließt, an einer Stelle, an der der Ausleger (13) ausgebildet werden soll. 25
10. Verfahren zum Herstellen eines Beschleunigungssensors gemäß dem Anspruch 4, worin dem fünften Schritt vorausgehend ein Schritt zum Bilden eines Halbleiterelements (10) auf dem ersten (1; 20) oder zweiten (8; 27) einkristallinen Siliziumsubstrat hinzugefügt wird. 30

11. Verfahren zum Herstellen eines Beschleunigungssensors, umfassend:

einen ersten Schritt zum Bondieren der Hauptoberfläche eines ersten einkristallinen Siliziumsubstrats (30; 42) an ein zweites einkristallines Siliziumsubstrat (32; 40), mit einem dazwischen eingesetzten isolierenden Film (33; 41);

einen zweiten Schritt zum Polieren der Oberfläche des ersten einkristallinen Siliziumsubstrats (30; 42) auf der Rückseite, die die der Hauptoberfläche davon gegenüberliegende Seite ist, bis zu einem vorbestimmten Grad, so, daß aus dem ersten einkristallinen Siliziumsubstrat ein dünner Film gemacht wird;

einen dritten Schritt zum Bilden eines Einschnittes in dem ersten einkristallinen Siliziumsubstrat (30; 42), wobei sich der Einschnitt in einer einen zu bildenden beweglichen Ausleger (13) umgebenden Fläche von der Rückseite des Substrats (30; 42) bis zu dem isolierenden Film (33; 41) erstreckt;

einen vierten Schritt zum Abscheiden eines Films (37) aus polykristallinem Silizium, amorphem Silizium oder einer Mischung daraus, von der Rückseite des ersten einkristallinen Siliziumsubstrats (30; 42) aus, so, daß der Einschnitt mit dem Siliziumfilm ausgefüllt wird, und zum Glätten der Oberfläche des Siliziumfilms; und

einen fünften Schritt zum Bilden einer Signalverarbeitungsschaltung (10) auf wenigstens einem von dem ersten und dem zweiten einkristallinen Siliziumsubstrat (30, 32; 40, 42), und danach Entfernen des Films (37) aus polykristallinem Silizium, amorphem Silizium oder einer Mischung daraus von der Rückseite des ersten einkristallinen Siliziumsubstrats (30; 42) aus, um den Ausleger (13) zu bilden.

12. Verfahren zum Herstellen eines Beschleunigungssensors gemäß dem Anspruch 11, worin im ersten Schritt der isolierende Film (33; 41) auf der Oberfläche des zweiten einkristallinen Siliziumsubstrats (32; 40) gebildet wird. 35
13. Verfahren zum Herstellen eines Beschleunigungssensors gemäß dem Anspruch 11, worin der fünfte Schritt einen Schritt zum Entfernen des isolierenden Films (41) an einer Stelle einschließt, die der Stelle, an der der Ausleger (13) gebildet wird, entspricht. 40

14. Verfahren zum Herstellen eines Beschleunigungs-

sensors gemäß dem Anspruch 11, worin der erste Schritt einen Schritt zum dem Bondieren vorhergehenden Bilden eines konkaven Teils (47) in einer Fläche der Hauptoberfläche des ersten einkristallinen Siliziumsubstrats (42) einschließt, die der Stelle, an der der Ausleger (13) gebildet werden soll, entspricht.

Revendications

1. Capteur d'accélération, caractérisé en ce qu'il comprend :

un second substrat de silicium monocristallin (8; 27; 32; 40) qui est lié à un premier substrat de silicium monocristallin (21; 30; 40), un film d'isolation (9; 28; 33; 41) étant interposé entre les substrats;

un profilé mobile (13), formé sur au moins un desdits premier ou second substrats de silicium monocristallin, et qui peut être déplacé dans une direction (C) parallèle à la surface du substrat; et

un circuit de traitement de signaux (10), formé sur au moins un desdits premier ou second substrats de silicium monocristallin pour exécuter le traitement de signaux produits par un mouvement dudit profilé causé par accélération.

2. Capteur d'accélération selon la revendication 1, dans lequel ledit profilé (13) est plus petit en épaisseur dans une direction parallèle à la surface desdits substrats de silicium monocristallin (1; 8; 20; 27; 30; 32; 40; 42) en comparaison avec l'épaisseur dans une direction de la profondeur desdits substrats de silicium monocristallin.

3. Capteur d'accélération selon la revendication 1, dans lequel au moins une des surfaces dudit profilé (13) et la surface du second substrat de silicium monocristallin (8; 27; 32; 40) face audit profilé sont couverts d'une isolation (5; 9; 25; 28; 33; 34).

4. Procédé pour la fabrication d'un capteur d'accélération, comportant :

une première étape de formation, sur une surface principale d'un premier substrat de silicium monocristallin (1; 20), d'une gorge d'une profondeur prédéterminée dans une zone entourant un profilé mobile (13) qui doit être formé;

une seconde étape de dépôt, sur la surface principale dudit premier substrat de silicium

monocristallin (1; 20), d'un film (6; 26) d'un silicium polycristallin, d'un silicium amorphe ou d'un mélange de ceux-ci, de manière à remplir la gorge avec ledit film de silicium, et de lissage de la surface dudit film de silicium;

une troisième étape de liaison de la surface principale dudit premier substrat de silicium monocristallin (1; 20) à un second substrat de silicium monocristallin (8; 27) avec un film d'isolation (9; 28) interposé entre eux;

une quatrième étape de polissage de la surface dudit premier substrat de silicium monocristallin (1; 20) sur son envers, qui est le côté opposé à la principale surface de celui-ci, à un degré prédéterminé de manière à faire du premier substrat de silicium monocristallin un film mince; et

une cinquième étape de formation d'un circuit de traitement de données (10) sur au moins l'un ou l'autre desdits premier et second substrats de silicium monocristallin (1; 8; 20; 27), et ensuite, de l'élimination par corrosion dudit film de silicium (6; 26) de silicium polycristallin, de silicium amorphe ou d'un mélange des deux dudit envers dudit premier substrat de silicium monocristallin (1; 20), pour former ledit profilé (13).

5. Procédé pour la fabrication d'un capteur d'accélération selon la revendication 4, dans lequel, dans ladite première étape, ladite profondeur prédéterminée est réglée selon l'épaisseur dudit profilé (13) dans la direction verticale de celui-ci.

6. Procédé pour la fabrication d'un capteur d'accélération selon la revendication 4, dans lequel, dans ladite troisième étape, ledit film d'isolation (9; 28) est formé sur la surface dudit second substrat de silicium monocristallin (8; 27).

7. Procédé pour la fabrication d'un capteur d'accélération selon la revendication 4, dans lequel, dans ladite seconde étape, il reste ledit film de silicium plat (6) sur la surface principale dudit premier substrat de silicium monocristallin (1).

8. Procédé pour la fabrication d'un capteur d'accélération selon la revendication 7, dans lequel, avant ladite troisième étape, il y a une étape supplémentaire pour rendre ledit film de silicium (6) restant sur la surface principale dudit substrat de silicium monocristallin (1) résistant à la corrosion dans ladite cinquième étape, à l'exception du film de silicium (6) positionné dans une zone entourant ledit profilé mobile (13).

9. Procédé pour la fabrication d'un capteur d'accélération selon la revendication 4, dans lequel ladite première étape comporte en plus une étape pour former une partie concave (21) sur la surface principale du premier substrat de silicium monocristallin (20) à l'endroit où ledit profilé (13) doit être formé.

10. Procédé pour la fabrication d'un capteur d'accélération selon la revendication 4, dans lequel avant ladite cinquième étape, il y a une étape supplémentaire pour former un élément semi-conducteur (10) sur ledit premier (1; 20) ou second (8; 27) substrat de silicium monocristallin.

11. Procédé pour la fabrication d'un capteur d'accélération comportant :

une première étape pour lier la surface principale d'un premier substrat de silicium monocristallin (30; 42) à un second substrat de silicium monocristallin (32; 40) avec un film d'isolation (33; 41) interposé entre-deux;

une seconde étape pour polir la surface dudit premier substrat de silicium monocristallin (30; 42) sur son envers, qui est le côté opposé à la surface principale de celui-ci, à un degré prédéterminé, de sorte à faire du premier substrat de silicium monocristallin un film mince;

une troisième étape pour former une gorge dans le premier substrat monocristallin (30; 42), la gorge s'étendant de l'envers du substrat (30; 42) audit film d'isolation (33; 41) dans une zone entourant le profilé mobile (13) qui doit être formé;

une quatrième étape pour déposer à partir de l'envers dudit premier substrat de silicium monocristallin (30; 42) un film (37) de silicium polycristallin, de silicium amorphe ou d'un mélange des deux, de manière à remplir ladite gorge au moyen dudit film de silicium, et pour lisser la surface dudit film de silicium; et

une cinquième étape pour former un circuit de traitement de signaux (10) sur au moins un desdits premier et second substrats de silicium monocristallin (30, 32; 40, 42), et ensuite éliminer par corrosion ledit film (37) de silicium polycristallin, de silicium amorphe ou d'un mélange des deux de l'envers dudit premier substrat de silicium monocristallin (30; 42), pour former ledit profilé (13).

12. Procédé pour la fabrication d'un capteur d'accélération selon la revendication 11, dans lequel, dans ladite première étape, ledit film d'isolation (33; 41)

est formé sur la surface dudit second substrat de silicium monocristallin (33; 40).

13. Procédé pour la fabrication d'un capteur d'accélération selon la revendication 11, dans lequel ladite cinquième étape comporte une étape d'élimination dudit film d'isolation (41) à un endroit correspondant à l'endroit où ledit profilé (13) est formé.

14. Procédé pour la fabrication d'un capteur d'accélération selon la revendication 11, dans lequel ladite première étape comporte une étape de formation, avant ladite liaison, d'une partie concave (47) dans une zone de la surface principale dudit premier substrat de silicium monocristallin (42) correspondant à l'endroit où ledit profilé (13) doit être formé.

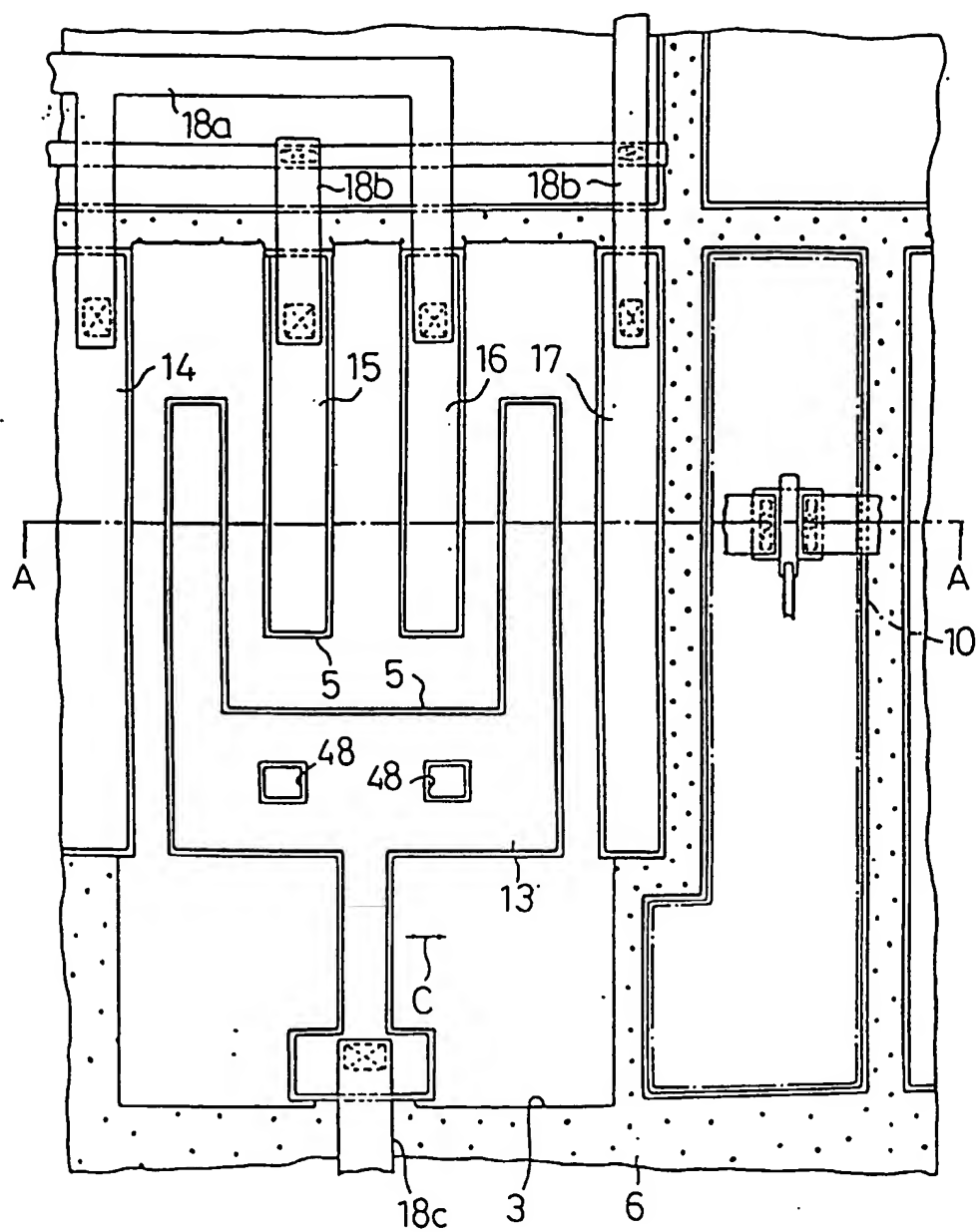


Fig. 1

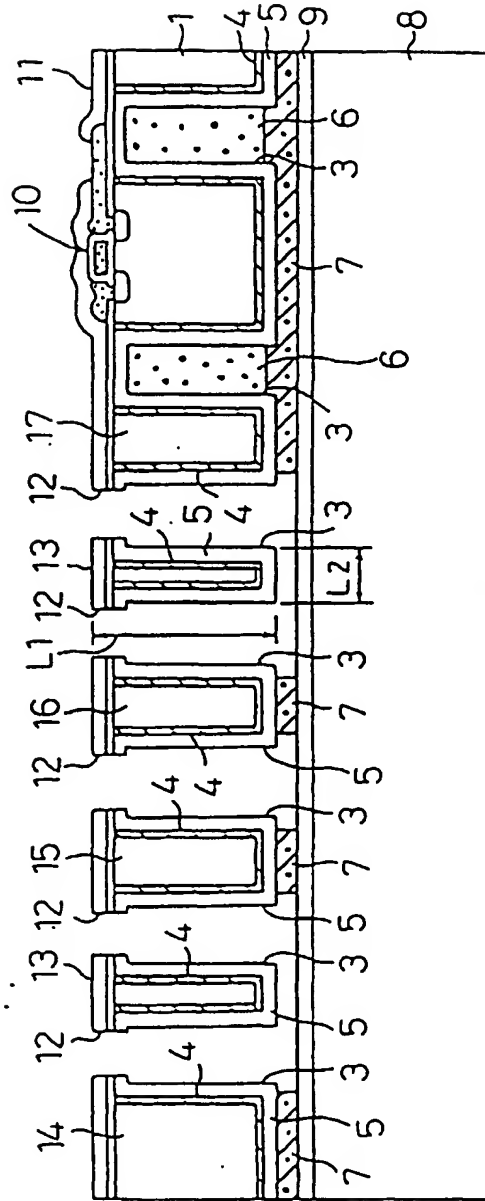


Fig. 2

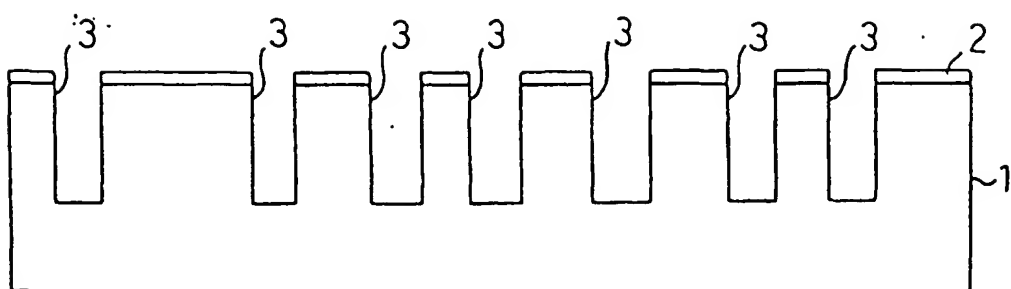


Fig. 3

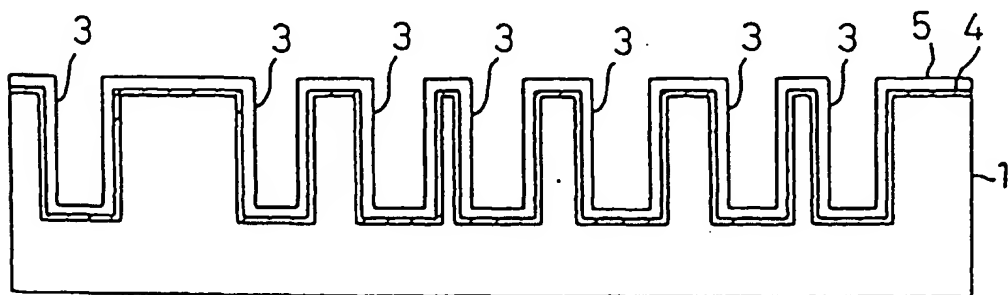


Fig. 4

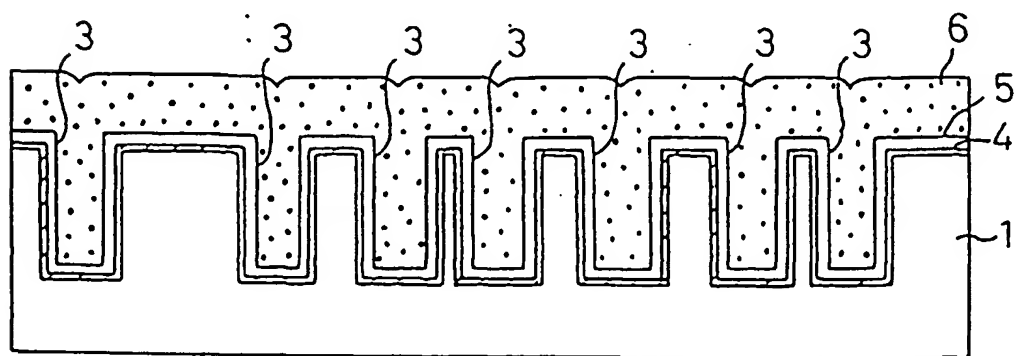


Fig. 5

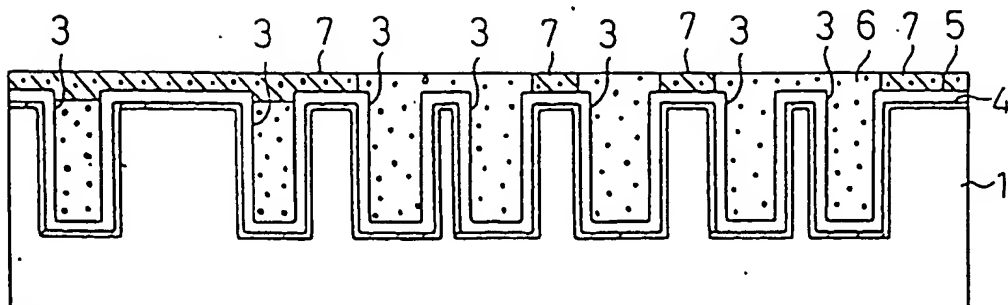


Fig. 6

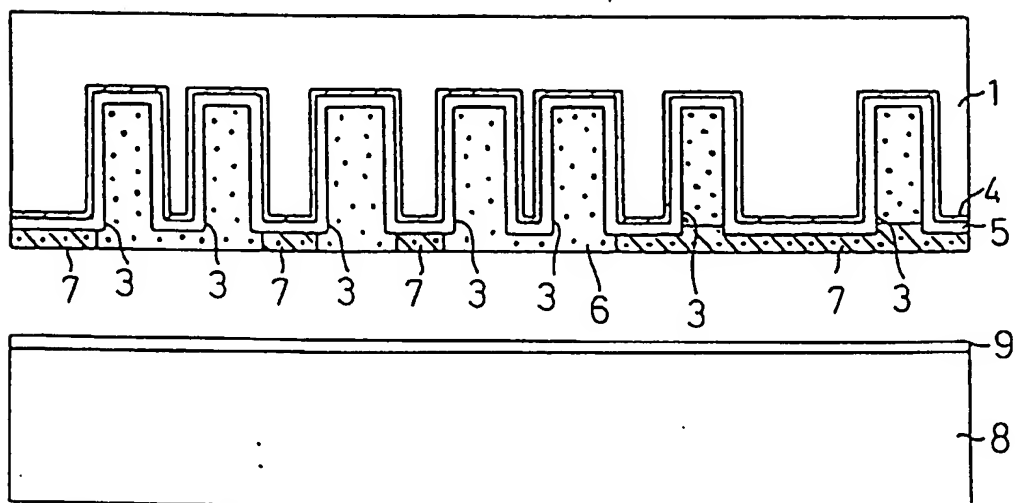


Fig. 7

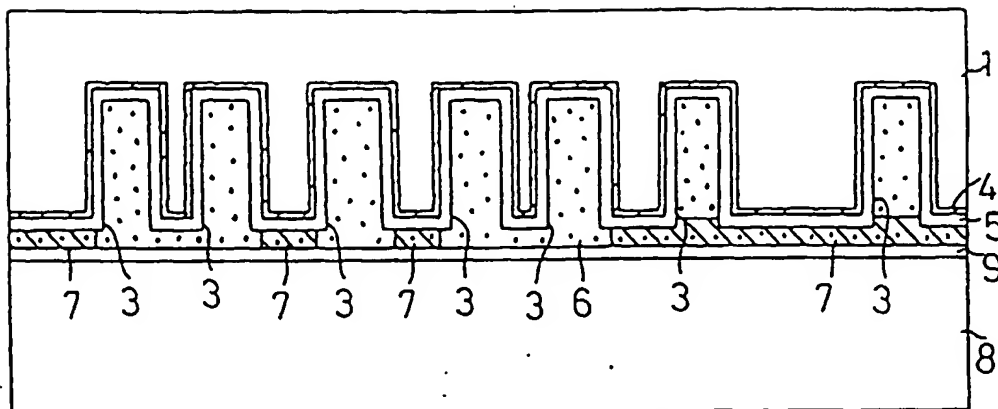


Fig. 8

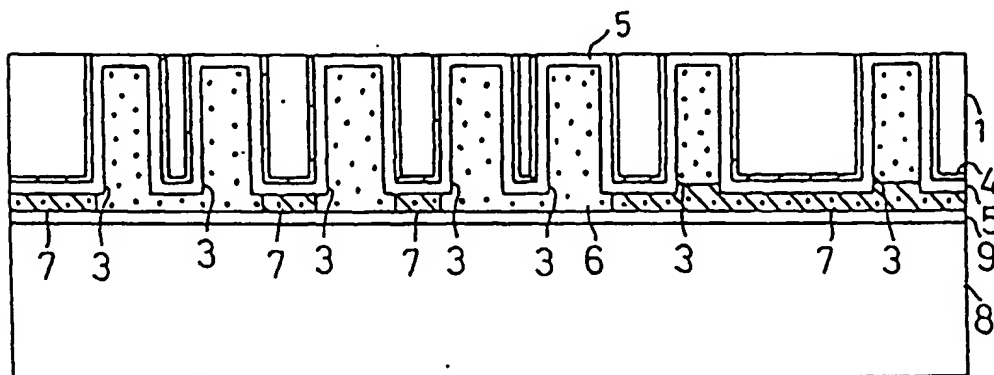


Fig. 9

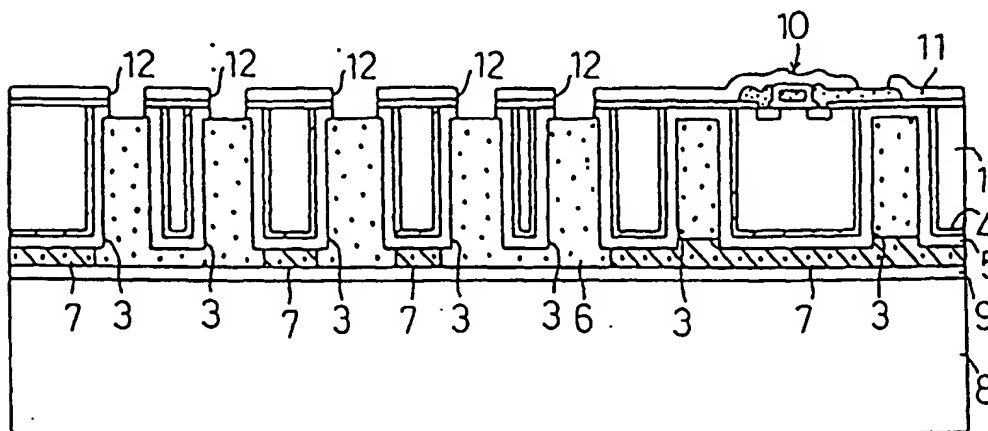


Fig. 10

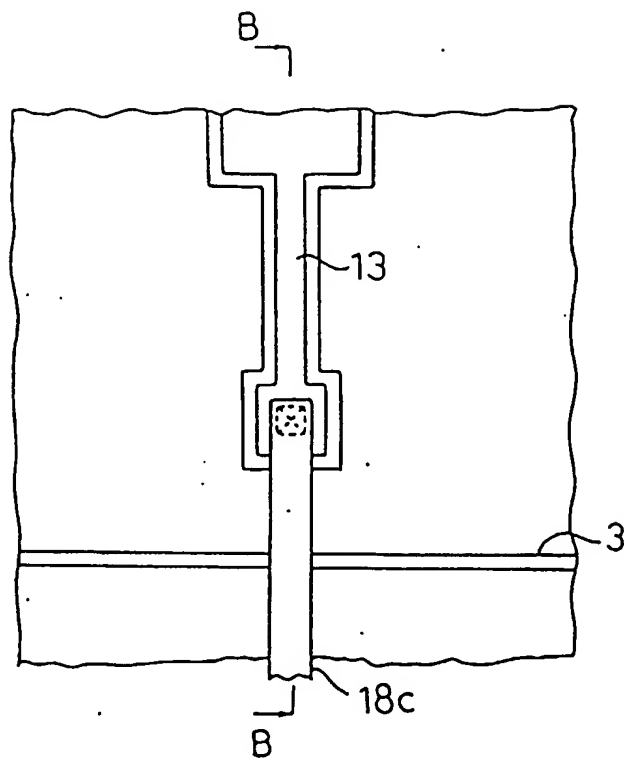


Fig. 11

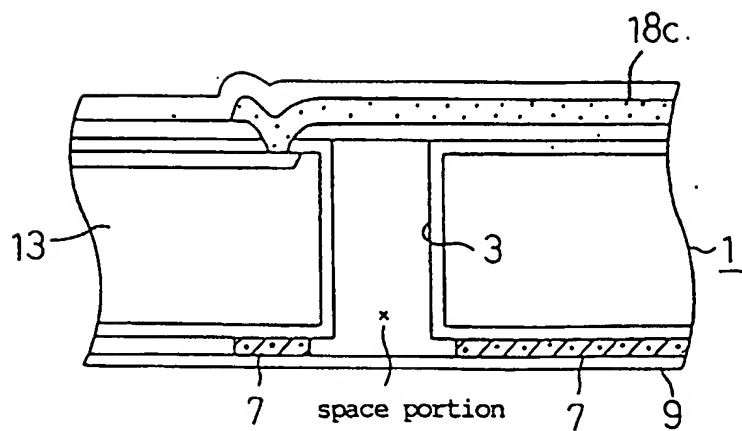


Fig. 12

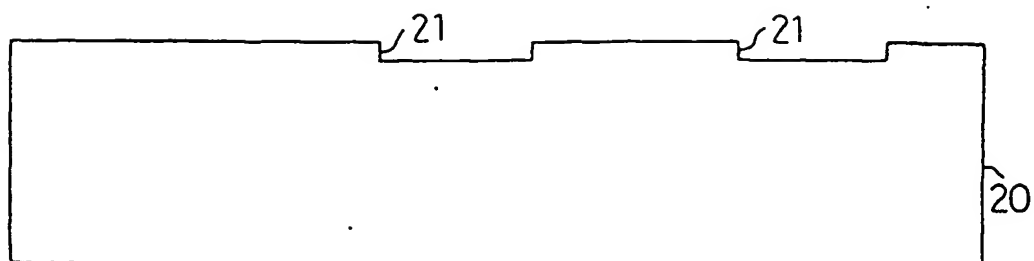


Fig. 13

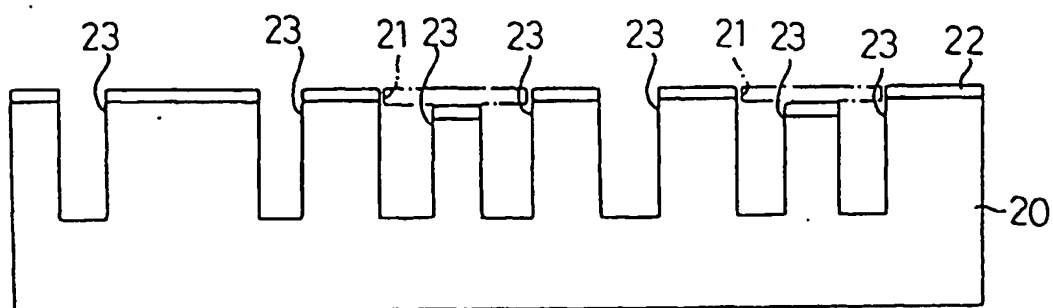


Fig. 14

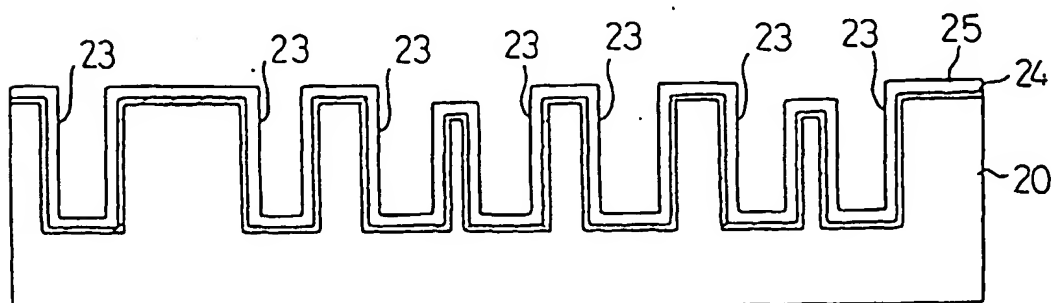


Fig. 15

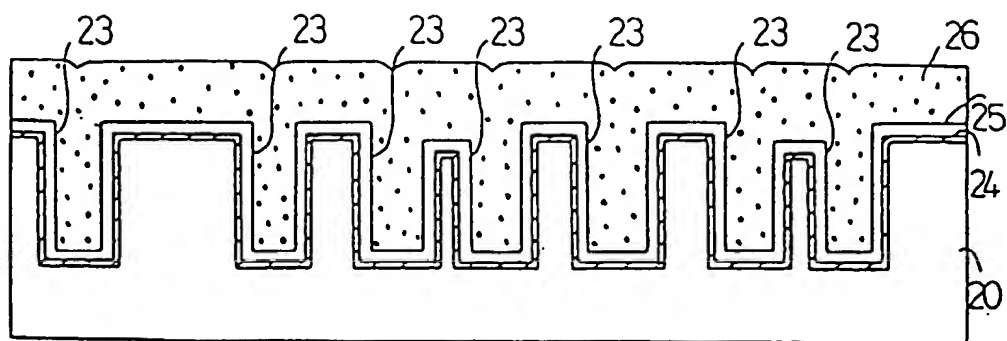


Fig. 16

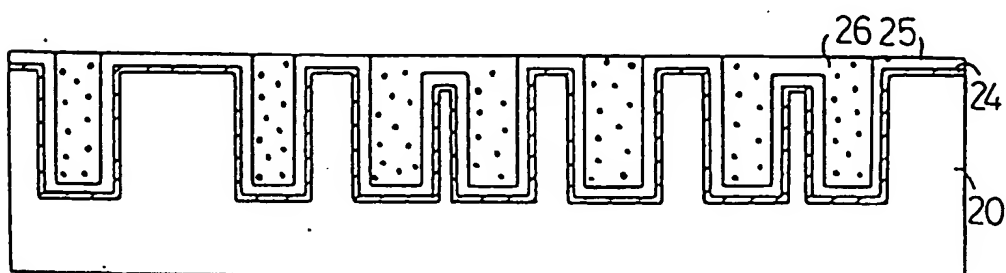


Fig. 17

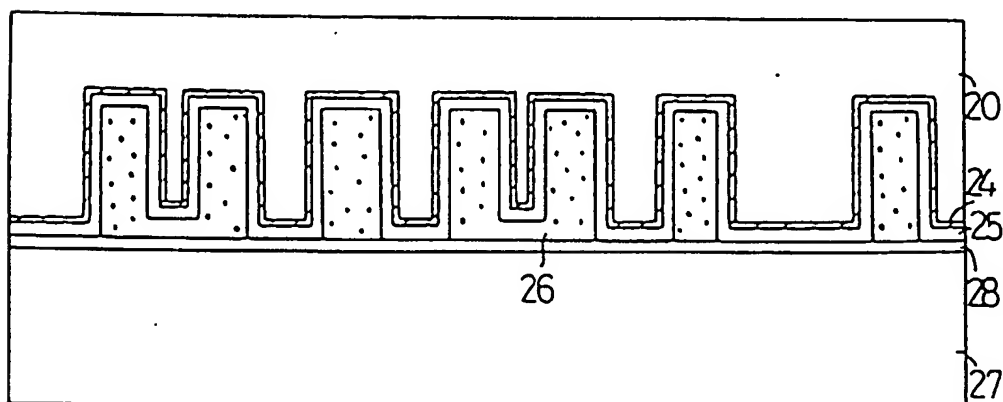


Fig. 18

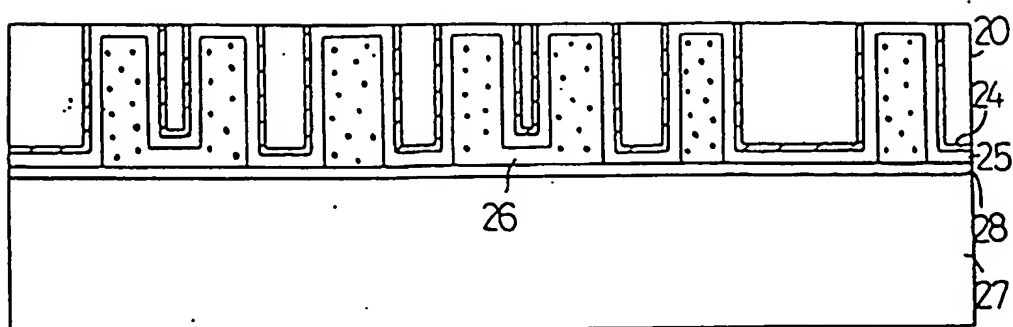


Fig. 19

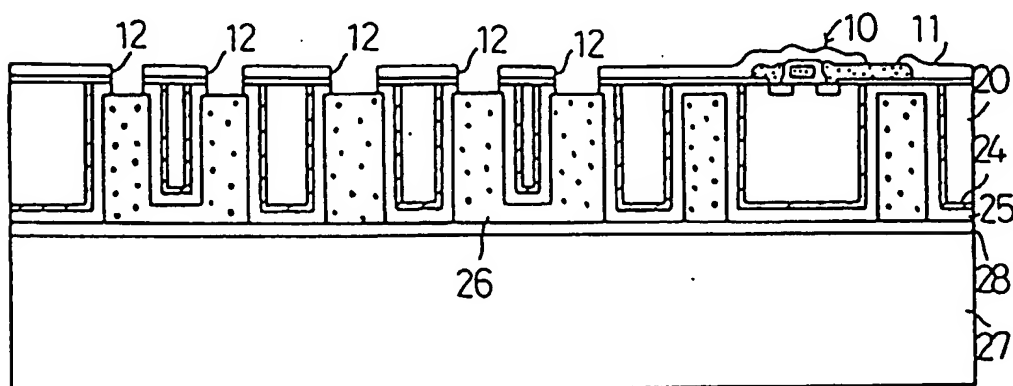


Fig. 20

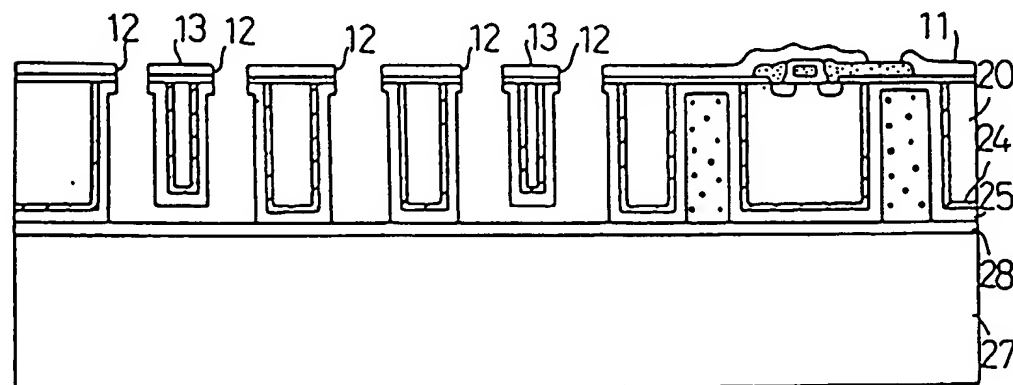


Fig. 21

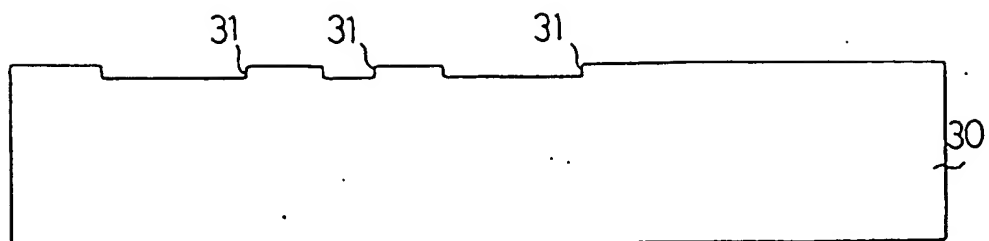


Fig. 22

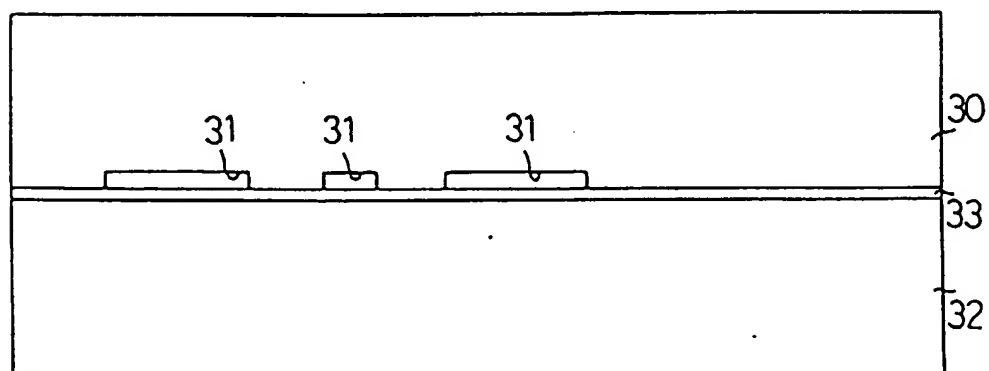


Fig. 23

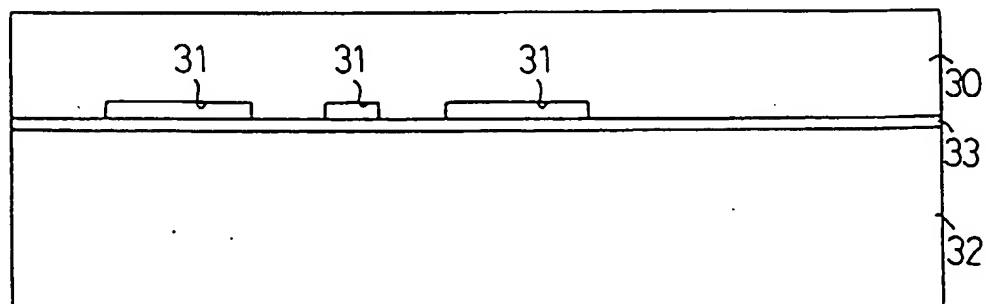


Fig. 24

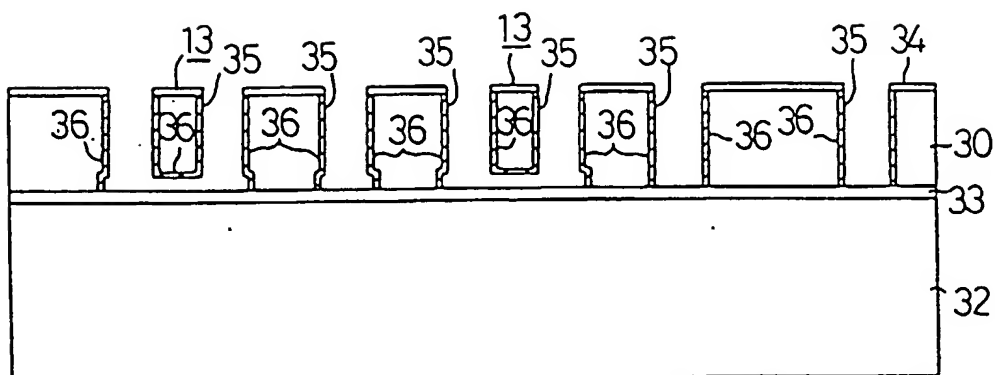


Fig. 25

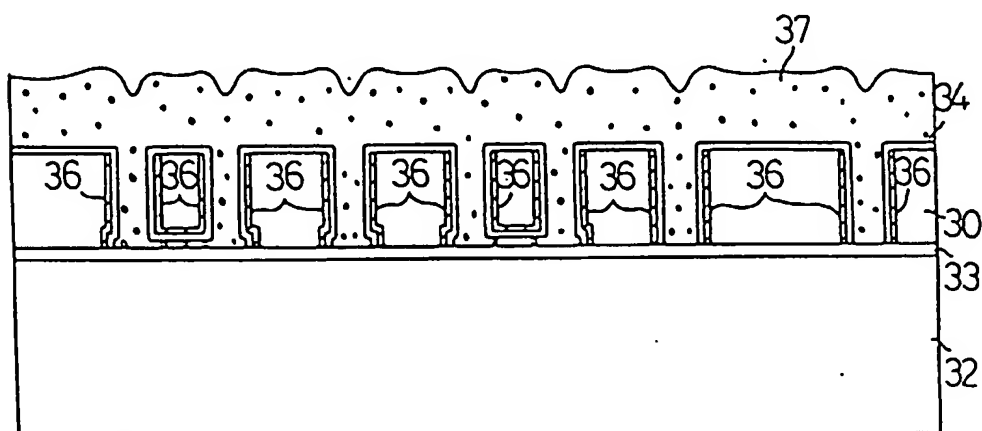


Fig. 26

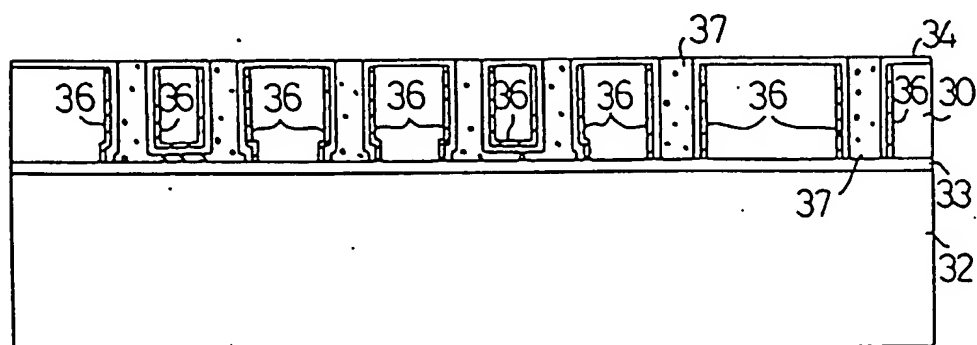


Fig. 27

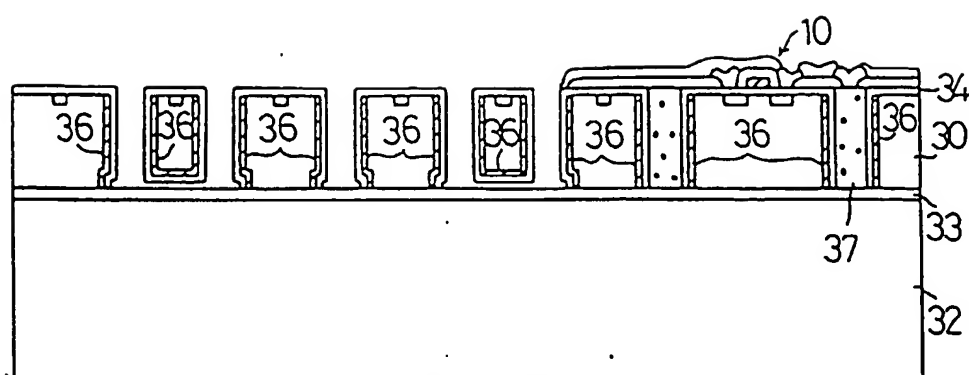


Fig. 28

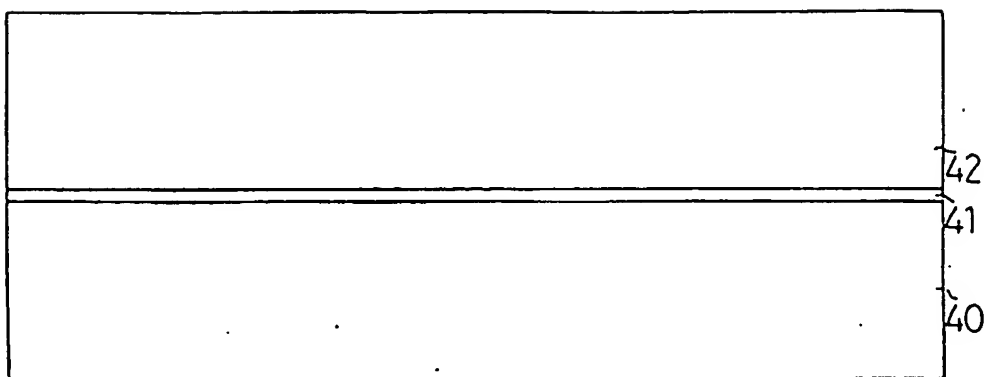


Fig. 29

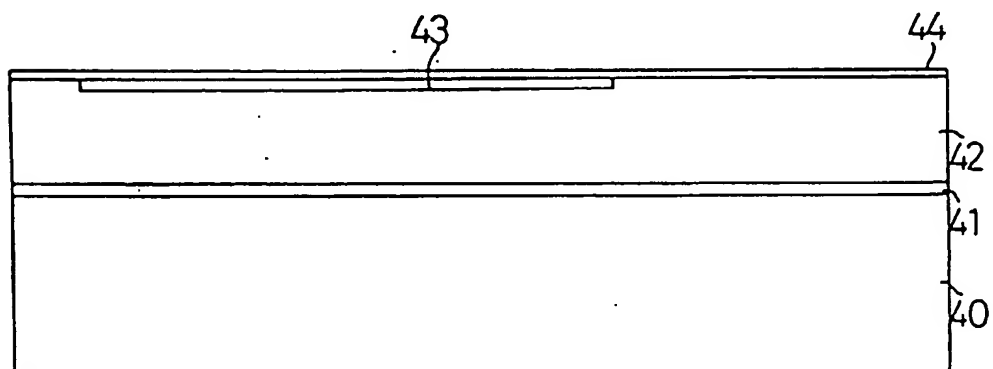


Fig. 30

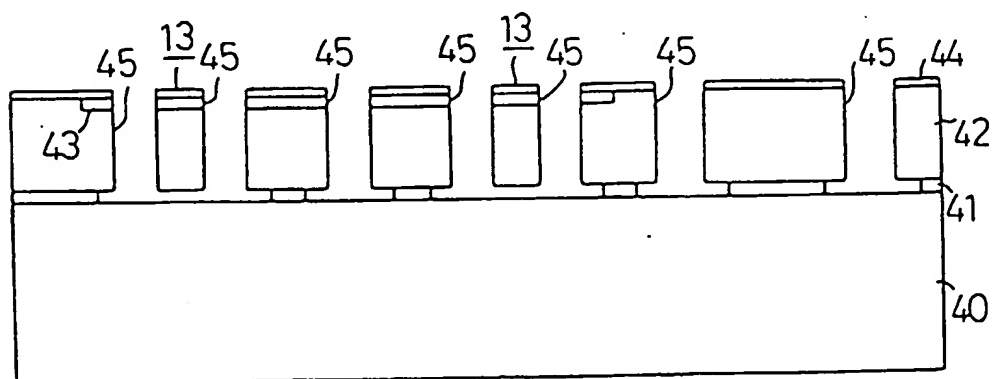


Fig. 31

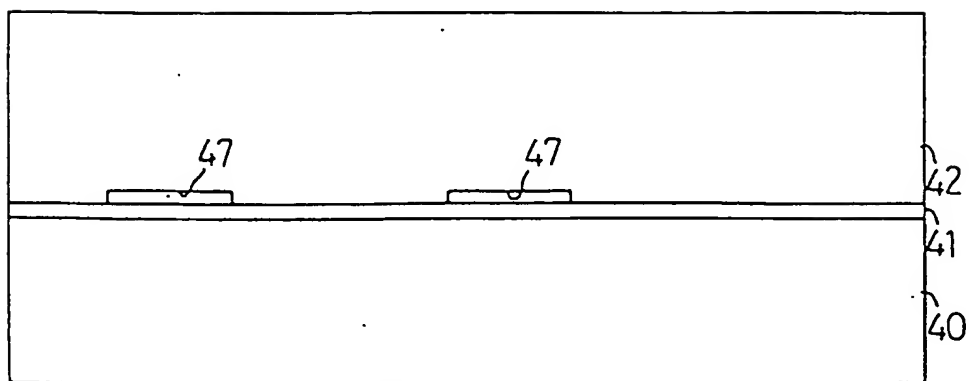


Fig. 32

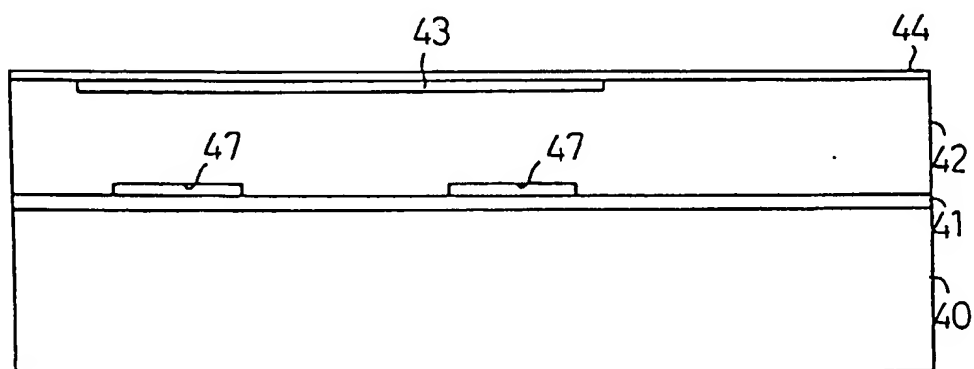


Fig. 33

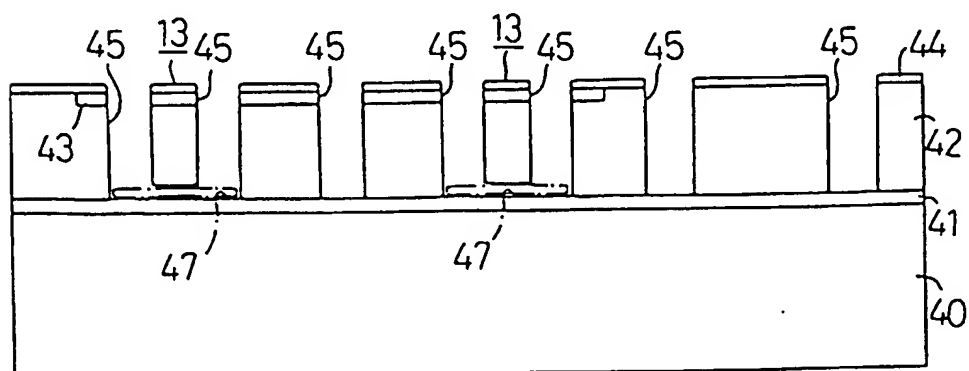


Fig. 34

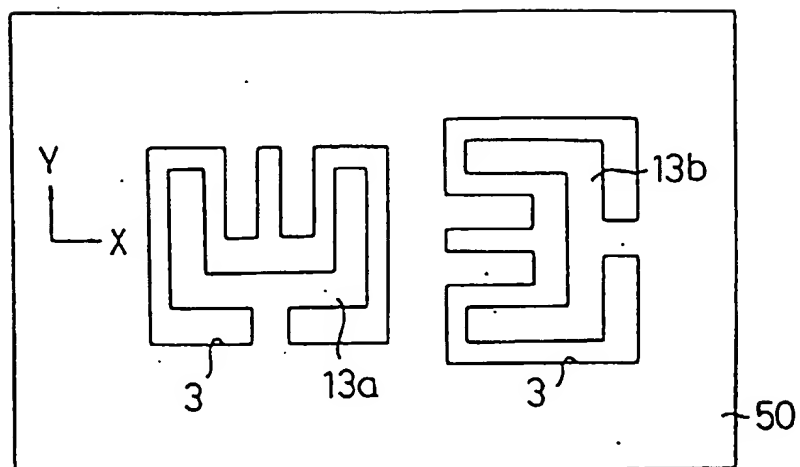


Fig. 35